

FORM PTO-1449		SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT		FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)		CONFIRMATION NO. 3451	

**REFERENCE DESIGNATION**      **U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER Number-Kind Code (if known)	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
	D1 3,901,423	08/1975	Hillberry, et al.		
	D2 3,915,757	10/1975	Engel		
	D3 3,957,107	05/1976	Altoz et al.		
	D4 3,993,909	11/1976	Drews et al.		
	D5 4,006,340	02/1977	Gorinas		
	D6 4,039,416	08/1977	White		
	D7 4,074,139	02/1978	Pankove		
	D8 4,107,350	08/1978	Berg et al.		
	D9 4,108,751	08/1978	King		
	D10 4,121,334	10/1978	Wallis		
	D11 4,170,662	10/1979	Weiss et al.		
	D12 4,179,324	12/1979	Kirkpatrick		
	D13 4,244,348	01/1981	Wilkes		
	D14 4,252,837	02/1981	Auton		
	D15 4,274,004	06/1981	Kanai		
	D16 4,324,631	08/1982	White et al.		
	D17 4,346,123	08/1982	Kaufmann		
	D18 4,361,600	11/1982	Brown		
	D19 4,368,083	01/1983	Bruel et al.		
	D20 4,412,868	11/1983	Brown et al.		
	D21 4,452,644	06/1984	Bruel et al.		
	D22 4,468,309	08/1984	White		
	D23 4,471,003	09/1984	Cann		
	D24 4,486,247	12/1984	Ecer et al.		
	D25 4,490,190	12/1984	Speri		
	D26 4,500,563	02/1985	Ellenberger et al.		
	D27 4,508,056	04/1985	Bruel et al.		
	D28 4,536,657	08/1985	Bruel		
	D29 4,539,050	09/1985	Kramler et al.		
	D30 4,542,863	09/1985	Larson		
	D31 4,566,403	01/1986	Fournier		
	D32 4,567,505	01/1986	Pease		
	D33 4,568,563	02/1986	Jackson et al.		
	D34 4,585,945	04/1986	Bruel et al.		
	D35 4,630,093	12/1986	Yamaguchi et al.		
	D36 4,684,535	08/1987	Heinecke et al.		
	D37 4,704,302	11/1987	Bruel et al.		

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449		SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT		FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)		APPLICANT(S): Nguyet-Phuong Nguyen et al.	

D38	4,717,683	01/1988	Parrillo et al.
D39	4,764,394	08/1988	Conrad
D40	4,837,172	06/1989	Mizuno et al.
D41	4,846,928	07/1989	Dolins et al.
D42	4,847,792	07/1989	Barna et al.
D43	4,853,250	08/1989	Boulos et al.
D44	4,887,005	12/1989	Rough et al.
D45	4,891,329	01/1990	Reisman et al.
D46	4,894,709	01/1990	Phillips et al.
D47	4,904,610	02/1990	Shyr
D48	4,920,396	04/1990	Shinohara et al.
D49	4,929,566	05/1990	Beitman
D50	4,931,405	06/1990	Kamijo et al.
D51	4,948,458	08/1990	Ogle
D52	4,952,273	08/1990	Popov
D53	4,956,698	09/1990	Wang
D54	4,960,073	10/1990	Suzuki et al.
D55	4,975,126	12/1990	Margail et al.
D56	4,982,090	01/1991	Wittmaack
D57	4,996,077	02/1991	Moslehi et al.
D58	5,013,681	05/1991	Godbey et al.
D59	5,015,353	05/1991	Hubler et al.
D60	5,034,343	07/1991	Rouse et al.
D61	5,036,023	07/1991	Dautremont-Smith et al.
D62	5,110,748	05/1992	Sarma
D63	5,120,666	06/1992	Gotou
D64	5,138,422	08/1992	Fujii et al.
D65	5,198,371	03/1993	Li
D66	5,200,805	04/1993	Parsons et al.
D67	5,232,870	08/1993	Ito et al.
D68	5,234,535	08/1993	Beyer et al.
D69	5,250,446	10/1993	Osawa et al.
D70	5,256,581	10/1993	Foerstner et al.
D71	5,259,247	11/1993	Bantien
D72	5,310,446	05/1994	Konishi et al.
D73	5,413,951	05/1995	Ohori et al.
D74	5,442,205	08/1995	Brasen et al.
D75	5,494,835	02/1996	Bruel
D76	5,524,339	06/1996	Gorowitz et al.
D77	5,539,241	07/1996	Abidi et al.
D78	5,567,654	10/1996	Beilstein, Jr. et al.
D79	5,611,316	03/1997	Oshima et al.

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609;  
Draw line through citation if not in conformance and not considered. Include copy of this form with next  
communication to applicant.

FORM PTO-1449		SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>		FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)		APPLICANT(S): Nguyet-Phuong Nguyen et al.	

D80	5,618,739	04/1997	Takahashi et al.
D81	5,622,896	04/1997	Knottner et al.
D82	5,633,174	05/1997	Li
D83	5,661,333	08/1997	Bruel et al.
D84	5,714,395	02/1998	Bruel
D85	5,741,733	04/1998	Bertagnolli et al.
D86	5,753,038	05/1998	Vichr et al.
D87	5,804,086	09/1998	Bruel
D88	5,817,368	10/1998	Hashimoto
D89	5,863,830	01/1999	Bruel et al.
D90	5,863,832	01/1999	Doyle et al.
D91	5,880,010	03/1999	Davidson
D92	5,882,987	03/1999	Srikrishnan
D93	5,897,331	04/1999	Sopori
D94	5,981,400	11/1999	Lo
D95	5,985,412	11/1999	Gösele
D96	6,010,591	01/2000	Gösele
D97	6,013,954	01/2000	Hamajima
D98	6,020,252	02/2000	Aspar et al.
D99	6,033,974	03/2000	Henley et al.
D100	6,054,363	04/2000	Sakaguchi et al.
D101	6,057,212	05/2000	Chan et al.
D102	6,080,640	06/2000	Gardner et al.
D103	6,096,433	08/2000	Kikuchi et al.
D104	6,118,181	09/2000	Merchant et al.
D105	6,156,215	12/2000	Shimada et al.
D106	6,159,323	12/2000	Joly et al.
D107	6,197,695 B1	03/2001	Joly et al.
D108	6,198,159 B1	03/2001	Hosoma et al.
D109	6,200,878 B1	03/2001	Yamagata et al.
D110	6,204,079 B1	03/2001	Aspar et al.
D111	6,225,192 B1	05/2001	Aspar et al.
D112	6,251,754 B1	06/2001	Ohshima et al.
D113	6,276,345 B1	08/2001	Nelson et al.
D114	6,287,940 B1	09/2001	Cole et al.
D115	6,294,478 B1	09/2001	Shkaguchi et al.
D116	6,306,720 B1	10/2001	Ding
D117	6,310,387 B1	10/2001	Seefeldt et al.
D118	6,316,333 B1	11/2001	Bruel et al.
D119	6,362,082 B1	03/2002	Doyle et al.
D120	6,407,929 B1	06/2002	Hale et al.
D121	6,417,075 B1	07/2002	Haberger et al.

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609;  
Draw line through citation if not in conformance and not considered. Include copy of this form with next  
communication to applicant.

FORM PTO-1449		SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>		FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)		APPLICANT(S): Nguyet-Phuong Nguyen et al.	

D122	6,429,094 B1	08/2002	Maleville et al.
D123	6,429,104 B1	08/2002	Auberton-Herve
D124	6,465,892 B1	10/2002	Suga
D125	6,504,235 B2	01/2003	Schmitz et al.
D126	6,529,646 B1	03/2003	Wight et al.
D127	6,548,375 B1	04/2003	De Los Santos et al.
D128	6,596,569 B1	07/2003	Bao et al.
D129	6,632,082 B1	10/2003	Smith
D130	6,645,831 B1	11/2003	Shaheen et al.
D131	6,645,833 B2	11/2003	Brendel
D132	6,653,207 B2	11/2003	Ohya et al.
D133	6,756,285 B1	06/2004	Moriceau et al.
D134	6,762,076 B2	07/2004	Kim et al.
D135	6,764,936 B2	07/2004	Daneman et al.
D136	6,774,010 B2	08/2004	Chu et al.
D137	6,809,009 B2	10/2004	Aspar et al.
D138	6,828,214 B2	12/2004	Notsu et al.
D139	6,846,690 B2	01/2005	Farcy et al.
D140	6,887,769 B2	05/2005	Kellar et al.
D141	6,893,936 B1	05/2005	Chen et al.
D142	6,902,987 B1	06/2005	Tong et al.
D143	6,927,147 B2	08/2005	Fitzgerald et al.
D144	6,947,365 B2	09/2005	Lai et al.
D145	6,974,759 B2	12/2005	Moriceau et al.
D146	6,991,956 B2	01/2006	Ghyselen et al.
D147	7,018,909 B2	03/2006	Ghyselen et al.
D148	7,029,548 B2	04/2006	Aspar et al.
D149	7,029,980 B2	04/2006	Liu et al.
D150	7,067,396 B2	06/2006	Aspar et al.
D151	7,078,811 B2	07/2006	Suga
D152	7,256,075 B2	08/2007	Ghyselen et al.
D153	7,348,260 B2	03/2008	Ghyselen
D154	7,416,957 B2	08/2008	Ponomarev
D155	7,459,374 B2	12/2008	Aulnette et al.
D156	7,465,646 B2	12/2008	Le Vaillant
D157	7,476,596 B2	01/2009	Lieber et al.
D158	7,494,897 B2	02/2009	Fournel et al.
D159	7,498,234 B2	03/2009	Aspar et al.
D160	7,521,292 B2	04/2009	Rogers et al.
D161	7,534,701 B2	05/2009	Ghyselen et al.
D162	7,615,463 B2	11/2009	Aspar et al.
D163	7,670,930 B2	03/2010	Tauzin et al.

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609;  
Draw line through citation if not in conformance and not considered. Include copy of this form with next  
communication to applicant.

FORM PTO-1449		SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT		FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)		APPLICANT(S): Nguyet-Phuong Nguyen et al.	

D164	7,713,369 B2	05/2010	Aspar et al.		
D165	7,772,087 B2	08/2010	Nguyen et al.		
D166	7,883,994 B2	02/2011	Moriceau et al.		
D167	7,902,038 B2	03/2011	Aspar et al.		
D168	RE39,484 E	02/2007	Bruel		
D169	2001/0007367 A1	07/2001	Ohkubo		
D170	2001/0007789 A1	07/2001	Aspar et al.		
D171	2002/0000646 A1	01/2002	Gooch et al.		
D172	2002/0081861 A1	06/2002	Robinson et al.		
D173	2002/0145489 A1	10/2002	Cornett et al.		
D174	2002/0185469 A1	12/2002	Podlesnik et al.		
D175	2002/0083387 A1	06/2002	Miner et al.		
D176	2002/0001221 A1	01/2003	Fischer et al.		
D177	2003/0119279 A1	06/2003	Enquist		
D178	2003/0119280 A1	06/2003	Lee et al.		
D179	2005/0148163 A1	07/2005	Nguyen et al.		
D180	2006/0252229 A1	11/2006	Joly et al.		
D181	2006/0281212 A1	12/2006	Moriceau et al.		
D182	2007/0037363 A1	02/2007	Aspar et al.		
D183	2008/0254591 A1	10/2008	Deguet et al.		
D184	2009/0120568 A1	05/2009	Deguet et al.		
D185	2009/0130392 A1	05/2009	Aspar et al.		
D186	2009/0156016 A1	06/2009	Di Cioccio		
D187	2010/0025228 A1	02/2010	Tauzin et al.		
D188	2010/0167499 A1	07/2010	Fournel et al.		
D189	2010/0216294 A1	08/2010	Rabarot et al.		
D190	2010/0323497 A1	12/2010	Fournel		

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER Number-Kind Code (if known)	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES OR NO
D191	EP 0 355 913 A1	02/1990	EPO		
D192	EP 0 383 391 A1	08/1990	EPO		
D193	EP 0 504 714 A2	09/1992	EPO		
D194	EP 0 660 140 A1	06/1995	EPO		ABSTRACT
D195	EP 0 665 588 A1	08/1995	EPO		ABSTRACT
D196	EP 0 703 609 A1	03/1996	EPO		ABSTRACT
D197	EP 0 754 953 B1	01/1997	EPO		ABSTRACT
D198	EP 0 849 788 A2	06/1998	EPO		
D199	EP 0 889 509 A2	01/1999	EPO		
D200	EP 0 895 282 A2	02/1999	EPO		
D201	EP 0 898 307 A1	02/1999	EPO		ABSTRACT

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449		SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>		FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)		APPLICANT(S): Nguyet-Phuong Nguyen et al.	

D202	EP 0 989 593 A2	03/2000	EPO		
D203	EP 1 059 663 A2	12/2000	EPO		
D204	EP 1 096 259 A1	05/2001	EPO		
D205	DE 101 53 319 A1	05/2003	GERMANY		ABSTRACT
D206	FR 95 08882	06/1996	FRANCE		ABSTRACT
D207	FR 2 558 263 A1	07/1985	FRANCE		ABSTRACT
D208	FR 2 671 472 A1	07/1992	FRANCE		ABSTRACT
D209	FR 2 725 074 A1	03/1996	FRANCE		ABSTRACT
D210	FR 2 736 934 A1	01/1997	FRANCE		ABSTRACT
D211	FR 2 767 604 A1	02/1999	FRANCE		ABSTRACT
D212	FR 2 771 852 A1	06/1999	FRANCE		ABSTRACT
D213	FR 2 789 518 A1	08/2000	FRANCE		ABSTRACT
D214	FR 2 819 099 A1	07/2002	FRANCE		ABSTRACT
D215	GB 2 211 991 A	07/1989	GREAT BRITAIN		
D216	JP 53-104156 A	09/1978	JAPAN		ABSTRACT
D217	JP 58-031519 A	02/1983	JAPAN		ABSTRACT
D218	JP 59-054217 A	03/1984	JAPAN		ABSTRACT
D219	JP 61-129872 A	06/1986	JAPAN		ABSTRACT
D220	JP 01-128570 A	05/1989	JAPAN		ABSTRACT
D221	JP 01-169917 A	07/1989	JAPAN		ABSTRACT
D222	JP 04-199504 A	07/1992	JAPAN		ABSTRACT
D223	JP 08-017777 A	01/1990	JAPAN		ABSTRACT
D224	JP 08-133878 A	05/1996	JAPAN		ABSTRACT
D225	JP 10-163166 A	06/1998	JAPAN		ABSTRACT
D226	JP 10-233352 A	09/1998	JAPAN		ABSTRACT
D227	JP 11-317577 A	11/1999	JAPAN		ABSTRACT
D228	SU 128757 A1	06/2000	RUSSIA		ABSTRACT
D229	WO 95/20824 A1	08/1995	WIPO		ABSTRACT
D230	WO 01/43168 A2	06/2001	WIPO		ABSTRACT
D231	WO 02/05344A1	01/2002	WIPO		ABSTRACT
D232	WO 03/021667 A2	03/2003	WIPO		
D233	WO 03/063213 A2	07/2003	WIPO		

<b>EXAMINER INITIAL</b>	<b>OTHER ART – NON PATENT LITERATURE DOCUMENTS</b> (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)		
	D234	Agarwal, Aditya et al. "Efficient Production of Silicon-On-Insulator Films by Co-Implantation of He <sup>+</sup> with H <sup>+</sup> " – Proceedings 1997 IEEE International SOI Conference, October 1997 – pp. 44-45.	
	D235	Ahn, K. Y., et al., "Growth, Shrinkage, And Stability of Interfacial Oxide Layers Between Directly Bonded Silicon Wafers", <i>Applied Physics A.</i> , Vol. 50, 1990, pp 85-94.	

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
	D236	Alley et al., "Surface Roughness Modification of Interfacial Contacts In Polysilicon Microstructures", Proceedings of the 7 <sup>th</sup> International Conference on Solid-State Sensors and Actuators, <i>Transducers '93</i> , PACIFICO, Yokohama JAPAN. Jun 7-10, 1993, pp 288-291.
	D237	Almedia et al. "Bond formation in ion beam synthesized amorphous gallium nitride", <i>Elsevier, This Solid Films</i> , 343-344 1999, pp 632-636.
	D238	Ascheron, C., "A Comparative Study of Swelling, Radiation, Strain and Radiation Damage of High-Energy Proton-bombarded GaAs, GaP, InP, Si and Ge Single Crystals, Nuclear Instruments and Methods in Physics Research", <i>Nuclear Instruments and Methods In Physics Research</i> B36, (1989), 163-172.
	D239	Ascheron, C., "A Study of Proton Bombardment Induced Swelling of GaP Single Crystals", <i>Phys. stat. sol. (a)</i> 92, (1985), pp 169-176.
	D240	Ascheron, C., "Getting a Copper in Proton-and Helium-Bombarded Buried Regions of Gallium Phosphide", <i>Phys. stat. sol. (a)</i> , Vol. 106, 1988, pp 73-79.
	D241	Ascheron, C., "Investigations of Hydrogen Implanted GaP Single Crystals by Means of Particle Induced 7-Spectroscopy, Infrared Spectroscopy, and Turyherford Backscattering Channeling Technique" <i>Phys. stat. sol. (a)</i> 89, (1985), pp 549.
	D242	Ascheron, C., "Proton Beam Modification of Selected AlIBV Compounds", <i>Phys. stat. sol. (a)</i> 124, (1991), pp 11.
	D243	Ascheron, C., "Swelling, Strain, and Radiation Damage of He+ Implanted GaP", <i>Phys. stat. sol. (a)</i> 96, 1986, pp. 555-562. (1986).
	D244	Asheran, C., "The Effect of Hydrogen Implantation Induced Stress on GaP Single Crystals", <i>Nuclear Instruments and Methods in Physics Research</i> , B28 (1987), pp 350-359.
	D245	Aspar et al., "The Generic Nature of the Smart-Cut <sup>®</sup> Process for Thin-Film Transfer", <i>Journal of Electronic Materials</i> , Vol. 30, No. 7, March - 2001, pp 834-840.
	D246	Aspar et al., Smart-Cut <sup>®</sup> : The basic fabrication process for UNIBOND <sup>®</sup> SOI wafers, <i>SEMI</i> 1996, pp. 37-46.
	D247	Aspar, B. "Basic Mechanisms Involved in the Smart-Cut Process", 1997, pp. 223-240.
	D248	Aspar, B. et al, "Characterization of SOI substrates: Application to Recent SIMOX and UNIBOND Wafers," <i>Electrochemical Society Proceedings</i> , vol. 96-3, pp. 99-111, January 1996.
	D249	Aspar, B. et al, "Transfer of Structured and Patterned Thin Silicon Films Using the Smart-Cut Process", 1996, pp. 1985-1986.
	D250	Aspar, B. Et al., "Ultra Thin Buried Oxide Layers Formed By Low Dose SIMOX Processes", Proc. 6 <sup>th</sup> International Conference on SOI Technology and Devices, <i>Electro. Soc.</i> , Vol. 94, No. 11, 1994, pp 62-69.

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
D251	Aspar, B. et al., "Smart Cut – Process Using Metallic Bonding: Application to Transfer of Si, GaAs, InP Thin Films", <i>Electronic Letters</i> – June 10, 1999, Vol. 35, No. 12., pp. 1024-1025.	
D252	Ashurst et al., "Water Level Anti-Silicon Coatings For MEMS", <i>Sensors and Actuators A104</i> , 2003, pp 213-221.	
D253	Auberton-Herve, A. J. et al, "A New Sal Material: Smart-Cut", 1996, pp.214-219.	
D254	Auberton-Herve et al., "SOI Materials for ULSI Applications", <i>Semiconductor International</i> , Oct. 1995, 5 pages.	
D255	Auberton-Herve, "Why Can Smart Cut® Change The Future Of Microelectronics?" published in <i>International Journal of High Speed Electronics and Systems</i> , Vol. 10, No. 1 (2000) pgs. 131-146.	
D256	Ayguavives et al., "Physical Properties of (Ba,Sr) TiO <sub>3</sub> Thin Films Used for Integrated Capacitors in Microwave Applications", <i>IEEE</i> 2001.	
D257	Blanchard-Lagache C. et al., "Hydrogen and Helium Implantation to Achieve Layer Transfer" Vol. 19, pp. 346-358, 2003, <i>Semiconductor Wafer Bonding VII: Science, Technology, and Applications – Proceedings of the International Symposium</i> .	
D258	Blöchl P.E. et al., "First-Principles Calculations of Diffusion Coefficients: Hydrogen in Silicon, <i>Physical Review Letters</i> , Vol. 64, No. 12, 1990, pp 1401-1404.	
D259	Borgati, Stephen P., "The Root-Mean-Square", Boston College, Nov. 16, 1998, Obtained from the Internet at: < <a href="http://www.analytictech.com/mb313/rootmean.htm">http://www.analytictech.com/mb313/rootmean.htm</a> >.	
D260	Bruel, Michel, "Application of Hydrogen Ion Beams To Silicon on Insulator Material Technology", <i>Nuclear Instruments and Methods in Physics Research</i> , B108, 1996, pp 313-319.	
D261	Bruel, M. et al., "Smart-Cut: A New Silicon on Insulator Material Technology Based on Hydrogen Implantation and Wafer Bonding", 1997, pp. 1636-1641, Col. 36, Part 1, No. 3B.	
D262	Bruel, M. "Smart-Cut Process: The Way to Unibond S.O.I. Wafers", 1996, pages unknown.	
D263	Bruel, M. et al, "Smart-Cut": A Promising New SOI material technology, <i>Proceedings 1994 IEEE, International Sal Conference</i> , Oct. 1995, pp. 178-179.	
D264	Bruel, M. et al, "Smart-Cut-a new SOI Material Technology based on hydrogen Implantation and wafer bonding," <i>CEA</i> , 1996, 24 pages.	
D265	Bruel, M., "Silicon on insulator Material Technology", <i>Electronic Letters</i> ; 31 (1995) Jul. 6; No. 14; pp. 1201-1202.	
D266	Bruel, M., "Silicon-an-Insulator", <i>European Semiconductor</i> , Mar. 1997.	
D267	Canham et al. "Radiative Recombination Channels due to Hydrogen In Crystalline Silicon", <i>Materials Science and Engineering</i> , B4 (1989) pp. 41-45.	
D268	Carter et al., "Applications of Ion Beams to Materials", <i>Inst. Phys. Conf. Ser.</i> , No. 28, Chapter 1, 1976, pp 30-36.	

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
D269	Carter, G. et al., "The Collection of Ions Implanted In Semiconductors: II Range Distributions Derived From Collection and Sputter-Etch Curves, <i>Radiation Effects</i> , 1972, Vol. 16, pp 107-114.	
D270	Cassidy, Victor M., "Ion Implantation Process Toughens Metalworking Tools," <i>Modern Metals</i> , 1984, pp. 65-67.	
D271	Cerofolini et al., "Hydrogen-Related Complexes as the Stressing Species in High-Fluence, Hydrogen-Implanted, Single-Crystal Silicon" <i>Physical Review B</i> , vol. 46, No.4, 1992, pp. 2061-2070.	
D272	Cerofolini et al., "Hydrogen and Helium Bubbles In Silicon", <i>Material Science and Engineering 2000 – Reports: A Review Journal</i> , Published By Elsevier Science S.A. 2000, pp. 1-52.	
D273	Chu et al, "Radiation Damage of 50-250 keV Hydrogen Ions in Silicon", <i>Ion Implantation in Semiconductors</i> , eds. F. Chernob et al., Plenum New York 1976, pp. 483-492.	
D274	Chu, et al. "Ion Implantation In Semiconductors", Chernow, Borders and Brice, Pirnum Press, New York and London. Radiation Damage of 50-250 keV Hydrogen Ions in Silicon, 1976, pp. 483-491.	
D275	Chu, P.K. et al., "Plasma Immersion Ion Implantation-A Fledgling Technique for Semiconductor Processing", <i>Materials Science and Engineering Reports</i> , A Review Journal, vol. R17, Nos. 6-7, Nov. 30, 1996, pp. 207-280.	
D276	Cowern, N. et al., "Transport Diffusion of Ion-Implanted B In Si: Dose, Time, and Matrix Dependence of Atomic and Electrical Profiles", <i>J. Appl. Phys.</i> , Vol. 68, No. 12, 1990, pp 6191-6198.	
D277	Cristoloveanu, S. et al, "Electrical Properties of Unibond Material", <i>Electrochemical Society Proceedings</i> , Vol. 96-3, pp. 142-147, 1996.	
D278	Csepregi, L. et al. "Regrowth Behavior of Ion-Implanted Amorphous Layers on <111> Silicon", <i>Applied Physics Letters</i> , Vol. 2, 1976, pp 92-93.	
D279	Cullis, A.G. et al. "Comparative study of annealed neon-, argon-, and krypton-ion implantation damage in silicon," <i>J. Appl. Phys.</i> , 49(10), Oct. 1978, pp. 5188-5198.	
D280	Denteneer, P. et al., "Hydrogen Diffusion and Passivation of Shallow Impurities in Crystalline Silicon, <i>Materials Science Forum</i> , Trans Tech Publications, Switzerland, Vols. 38-41, 1989, pp 979-984.	
D281	Denteneer, P. et al., "Structure and Properties of Hydrogen-Impurity Pairs in Elemental Semiconductors", <i>Physical Review Letters</i> , Vol. 62, No. 16, 1989, pp 1884-1888.	
D282	Di Cioccio, L. et al., "Silicon Carbide On Insulator Formation By The Smart Cut® Process". – <i>Materials Science and Engineering B46</i> (1997) – (pgs. 349-356).	
D283	DiCioccio, et al., "Silicon carbide on Insulator formation using the Smart Cut process", <i>Electronics Letters</i> , vol. 32, No. 12, Jun. 6, 1996, pp. 1144-1145.	

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
D284	Diem et al., "SOI 'SIMOX': From Bulk To Surface Micromachining, A New Age For Silicon Sensors and Actuators", <i>Sensors and Actuators</i> , Vol. A 46-47, 1995, pp 8-16.	
D285	Dirks, A. G. et al., "Columnar Microstructure In Vapor DEuropested Thin Films ", <i>Thin Solid Films</i> , Vol. 47, 1977, pp 219-233.	
D286	Donohue et al., "Pulse-Extended Excimer Laser Annealing of Lead Zirconate Titanate Thin Films", Proceedings of the 12 <sup>th</sup> International Symposium on Integrated Ferroelectrics, Aachen, Germany, March 2000, <i>Integrated Ferroelectrics</i> , vol. 31, pages 285 to 296, 2000.	
D287	Duo, et al., "Comparison Between The different Implantation orders in H+ and He+ Co-implantation", <i>J. Phys. D. Appl. Phys.</i> Vol. 34, 2001, pp 477-482.	
D288	Duo, et al., "Evolution of Hydrogen and Helium Co-Implanted Single-Crystal Silicon During Annealing", 2001 American Institute Physics – Journal of Applied Physics, Vol. 90, No. 8, October 15, 2001, pp. 3780-3786.	
D289	Eaglesham, White, Feldman, Moriya And Jacobson, "Equilibrium Shape of Si," <i>Physical Review Letters</i> , vol. 70, No. 11, Mar. 15, 1993, pp. 1643-1646.	
D290	EerNisse, E., "Compaction of ion-implanted fused silica", <i>Journal of Applied Physics</i> , vol. 45, No.1, Jan. 1974.	
D291	EerNisse, E.P., "Role of Integrated Lateral Stress In Surface Deformation of He- Implanted Surfaces" <i>Journal of Applied Physics</i> , vol. 48, No.1, Jan. 1977, pp 9-17.	
D292	Evans, J.H., "An Interbubble Fracture Mechanism Of Blister Formation On Helium- Irradiated Metals" <i>Journal of Nuclear Materials</i> , 68, 1977, pp 129-140.	
D293	Fujitsuka et al., "A New processing Technique To Prevent Stiction Using Silicon Selective Etching For SOT-MEMS", <i>Sensors and Actuators</i> , A97-98, 2002, pp 716- 719.	
D294	Garnier, D. M., "The Fabrication Of A Partial Soi Substrate", Proceedings of the 9 <sup>th</sup> International Symposium On Silicon On Isolator Technology and Devices, Vol. 99, Chap. 54, 1990, 73-78.	
D295	Gerasimenko, N., "Infrared Absorption of Silicon Irradiated by Protons", <i>Phys. stat.sol. (b)</i> 90, (1978), pp 689-695.	
D296	Ghandi, Sorab, "VLSI Fabrication Princiles-Silicon And Gallium Arsenide", <i>Rensselaer Polytechnic Institute</i> , 1983, John Wiley & Sons publishers, pp 135.	
D297	Goesele et al., "Semiconductor Wafer Bonding", Science and Technology, ECS Series, <i>Annual Review of Material Science</i> , Vol, 28, New Jersey, 1999, pp 215-241.	
D298	Greenwald, A.C., "Pulsed-electron-beam annealing of ion-implantation damage", <i>J. Appl. Phys.</i> 50(2), Feb. 1978, pp. 783-786.	
D299	Grovenor, C.R.M., <i>Microelectronic Materials</i> , pp. 73-75 (1989).	
D300	Guilhalmenc, C. et al, "Characterization By Atomic Force Microscopy of the SOI Layer Topography in Low Dose SIMOX Materials", <i>Materials Science and Engineering</i> , B46, 1997, pp 29-32.	

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
	D301	Haisma et al., Silicon-on-Insulator Wafer Bonding-Wafer Thinning Technological Evaluations", <i>JAPANese Journal of Applied Physics</i> , 28, 1989, Aug., No.8, Part 1, Tokyo, JAPAN, pp. 1426-1443.
	D302	Hamaguchi et al., "Device Layer Transfer Technique using Chemi-Mechanical Polishing", <i>JAPANese Journal of Applied Physics</i> , 23,(1984), Oct., No. 10, Part 2, Tokyo, JAPAN, pp. L815-L817.
	D303	Heistand et al., "Advances in Passive Integration for C/RC Arrays & Networks with Novel Thin & Thick Film Materials", 36 <sup>th</sup> Nordic IMAPS Conference, Helsinki, 1999.
	D304	Hendrix et al., "Low-Temperature Process for High-Density Thin-Film Integrated Capacitors", International Conference on High-Density Interconnect and Systems Packaging, 2000.
	D305	Huang, et al., "Calculation of critical layer thickness considering thermal strain in Si <sub>1-x</sub> Ge <sub>x</sub> /Si strained-layer heterostructures, <i>J. Appl. Phys.</i> 83 (1), January 1, 1998.
	D306	Hulett, D.M. et al., "Ion Nitriding and Ion Implantation: A Comparison," <i>Metal Progress</i> , 1985, pp. 18-21.
	D307	IBM Technical Disclosure Bulletin, <i>Isolation by Inert Ion Implantation</i> , 1986, vol. 29 No. 3, pp 1416.
	D308	IBM Technical Disclosure Bulletin, <i>SOI Interposer Structure XP 000627972</i> , July 1996, vol. 39 No. 7, pp. 1-5.
	D309	Jalaguier, E. et al., "Transfer of Thin InP Films Onto Silicon Substrate By Proton Implantation Process". – 11 <sup>th</sup> International Conference on Indium Phosphide and Related Materials 16-20 May 1999 – Davos, Switzerland. (pgs. 26-27)
	D310	Jalaguier, E. et al., "Transfer of 3in GaAs Film on Silicon Substrate By Proton Implantation Process". – (2 pgs).
	D311	Jaussaud, C. et al., 'Microstructure of Silicon Implanted With High Dose Oxygen Ions", <i>Appl. Phys. Lett.</i> , Vol. 48, No. 11, 1985, pp 1064-1066.
	D312	Jenei et al., "High-Q Inductors and Capacitors on Si Substrate", IEEE 2001.
	D313	Johnson, "High Fluence Deuteron Bombardment of Silicon", <i>Radiation Effects</i> , vol. 32, pp. 159-167, 1977.
	D314	Jones, K. S. et al., "A Systematic Analysis of Defects In Ion Implanted Silicon", <i>Applied Physics A.</i> , Vol. 45, 1988 pp 1-34.
	D315	Jones et al., "Enhanced elimination of implantation damage upon exceeding the solid solubility", <i>J. App. Phys.</i> , Vol. 62, No. 10, 1987, pp 4114-4117.
	D316	Kamada et al, "Observation of Blistering and Amorphization on Germanium Surface After 450 keV Ar+ION Bombardment, <i>Radiation Effects</i> , vol. 28, 1976, pp. 43-48.
	D317	Kim et al., "A Porous-Si-based Novel Isolation Technology for Mixed-Signal Integrated Circuits", <i>Symposium on VLSI Technology</i> , 2000.

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
	D318	Klem, J.F., "Characteristics of Lift-Off Fabricated AlGaAs/InGaAs Single-Strained-Quantum Well Structures On Glass and Silicon Substrates", <i>Inst. Phys. Conf. Ser.</i> No. 96: Chapter 6, (1989), pp. 387-392.
	D319	Komarov et al., "Crystallographic Nature and Formation Mechanisms of Highly Irregular Structure in Implanted and Annealed S1, LayersRadiation Effects, vol. 42, 1979, pp. 169-178.
	D320	Laporte A. et al., "Charged Defects At The Interface Between Directly Bonded Silicon Wafers" – <i>Applied Physics</i> , Vol. 36 (September 1997) pp. 5502-5506-Part 1, No. 9A.
	D321	Li, J., "Novel Semiconductor Substrate Formed by Hydrogen Ion Implantation into Silicon," <i>Appl. Phys. Lett.</i> , vol. 55, No. 21, Nov. 20, 1989, pp. 2223-2224.
	D322	Ligeon, E., "Hydrogen Implantation in Silicon Between 1.5 and 60 KeV", <i>Radiation Effects</i> 1976, vol. 27, pp. 129-137.
	D323	Liu et al., "Investigation of Interface In Silicon-On-Insulator By Fractual Analysis", <i>Applied Surface Science</i> , Vol. 187, Feb 28, 2002, pp 187-191.
	D324	Liu et al., "Integrated Thin Film Capacitor Arrays", International Conference on High Density Packaging and MCMs, 1999.
	D325	Lu, X., et al., "SOI Material Technology Using Plasma Immersion ION Implantation", <i>Proceedings 1996 IEEE International SOI Conference</i> , October 1996, pp. 48-49.
	D326	Maleville, C. et al, "Physical Phenomena involved in the Smart-Cut Process", <i>Electrochemical Society Proceeding</i> , vol. 96-3, 1996 - pp. 34-46.
	D327	Maleville, C. et al, "Wafer Bonding and Hi-Implantation Mechanisms Involved In The Smart-Cut Technology", 1997, pp 14-19.
	D328	Manuaba, A., "Comparative Study on Fe32Ni36Cr14P12B 6 Metallic Glass and its Polycrystalline Modification bombarded by 2000 keV Helium Ions with High Fluence" <i>Nuclear Instruments and Methods</i> , (1982) pp 409-419.
	D329	Mastrangelo, C. et al., "Suppression of Stiction in MEMS", <i>Proceedings of the Materials Research Society Seminar</i> , Vol. 605, 2000, pp 1-12.
	D330	Matsuda et al., "Large Diameter Ion Beam Implantation System," <i>Nuclear Instruments and Methods</i> , vol. B21, 1987, pp. 314-316.
	D331	Matsuo et al., "Abnormal solid solution and activation behavior in GA-implanted Si(100)", <i>Appl. Phys. Lett.</i> , Vol. 51, No. 24, 1987, pp 2037-2039.
	D332	Mishima, Y. and T. Yagishita, T. "Investigation of the bubble formation mechanism in a-Si:H films by Fourier-transform infrared microspectroscopy" <i>J. Appl. Phys.</i> , vol. 64, No.8, Oct. 15, 1988, pp3972-3974.
	D333	Miyagawa, S. et al, "Helium Reemission During Implantation of Silicon Carbide", <i>J. Appl. Phys.</i> , 54 (5), May 1983, pp. 2302-2306.
	D334	Miyagawa, S., "Surface structure of silicon carbide Irradiated with helium ions with mono energy and continuous energy distributions" <i>J. Appl. Phys.</i> 53(12), Dec. 1982, pp. 8697-8705.

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
D335	Monemar, B. "Shallow Impurities in Semiconductors 1998", Proceedings of the Third International Conference in Sweden, Aug. 10-12, 1988, No. 95, pp 493-499.	
D336	Moreau, Wayne M., "Semiconductor Lithography, Principles, Practices, and Materials," Plenum Press, 1988. Table of Contents only. Moriceau, H. et al, A New Characterization Process Used to Qualify SOI Films 1991 pp. 173-178.	
D337	Moriceau, H. et al, "A New Characterization Process Used to Qualify SOI Films", Electrochemical Society Proceedings, Volume 99-3, 1999 pp. 173-178.	
D338	Moriceau, H. et al, "A New Characterization Process Used to Qualify SOI Films", Abstract No. 405, Meeting Abstracts, The Electrochemical Society, Inc., Vol. 99-1, Seattle, May 2-6, 1999, 2 pages.	
D339	Moriceau, H. et al. "Cleaning and Polishing As Key Steps For Smart-Cut SOI Process", Proceedings 1996 IEEE SOI Conference, Oct. 1996.	
D340	Moriceau, H. et al, "The Smart-Cut Process as a Way to Achieve Specific Film Thickness in Sal Structures", 1997, pages unknown.	
D341	Motohiro et al. "Geometrical Factors of Argon Incorporation In $SiO_2$ Films Deposited By ION Beam Sputtering" – Thin Solid Films, Elsevier-Sequoia S.A. Lausanne, CH, Vol. 120, No. 4 – October 1, 1984 (1984-10-01), pgs. 313-327.	
D342	Munteanu, D. et al, "Detailed Characterization of Unibond Material", 1997, pp. 395-398.	
D343	Myers, D. R., "The effects of Ion-Implantation damage on the first order Raman spectra GaPa)" <i>J. Appl. Phys.</i> 54(9), Sep. 1977.	
D344	Nethling. J. et al, "Identification of Hydrogen Platelets in ProtonBombarded GaAs", 1985, pp. 941-945.	
D345	Nichols C. S et al., "Properties of Hydrogen in Crystalline Silicon Under Compression and Tension", <i>Physical Review Letters</i> , Vol. 63, No. 10, 1989, pp 1090-1093.	
D346	Nicoletti, S. et al., "Bi-Epitaxial YBCO Grain Boundry Josephson Junctions on SrTiO <sub>3</sub> and Sapphire Substrates", <i>Physics</i> C269, 1996, pp 255-267.	
D347	Ono et al., "Orientation Dependence of Flaking of Ion Irradiated Aluminum Single Crystals", <i>Japanese Journal of Applied Physics</i> , vol. 25, No., 10, 1986, pp. 1475-1480.	
D348	Paszti, E, "Flaking and Wave-Like Structure on Metallic Glasses Induced by MeV-Energy Helium Ions", <i>Nuclear Instruments and Methods</i> , Vol. 209/210, (1983), pp. 273-280.	
D349	Picraux, S. Thomas et al., "Ion Implantation of Surfaces," <i>Scientific American</i> , vol. 252, No.3, pp. 102-113 1985.	
D350	Popov, V.P. et al., "Blistering On A Silicon Surface in the Process of Sequential Hydrogen/Helium ION Co-Implantation" – Optoelecironics Instrumentation and Data Processing, No. 3, April 5, 2001 - pp. 90-98 – 2001.	
D351	Primak, W., "Impurity Effect in the Ionization Dilation of Vitreous Silica" <i>J. Appl. Phys.</i> 39(13) 1968.	

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
	D352	Ray et al. "Effect of Reactive-Ion Bombardment on the Properties of Silicon Nitride and Oxynitride Films Deposited By Ion-Beam Sputtering" – Journal of Applied Physics, Vol. 75, No. 12, June 15, 1994 – pgs. 8145-8152.
	D353	Renier, M. et al., "A New Low-Energy Ion Implanter for Bombardment of Cylindrical Surfaces," Vacuum, vol. 35, No. 12, pp. 577-578, 1985.
	D354	Roozeboom et al., "High-Value MOS Capacitor Arrays in Ultradeep Trenches in Silicon", <i>Microelectronic Engineering</i> , vol. 53, pages 581 to 584, Elsevier Science 2000.
	D355	Roth, J., "Blistering and Bubble Formation" <i>Inst. Phys. Conf. Ser.</i> No. 28, 1976: Chapter 7, pp 280-293.
	D356	Sah, Chih -Tang et al., "Deactivation of the Boron Acceptor in Silicon by Hydrogen," <i>Appl. Phys. Lett.</i> 43, (2), Jul. 1983, pp. 204-206
	D357	Saint-Jacques R. G., "La Formation des Cloques", <i>Nuclear Instruments and Methods</i> , No. 209/210", North Holland Publishing Co., 1983, pp 333-343.
	D358	Schnell et al., "Plasma Surface Texturization for Multicrystalline Silicon Solar Cells", <i>IEEE, XXVIII, Photovoltaic Conference</i> , 2000, pp 367-370.
	D359	Shintani, A. et al., "Temperature dependence of stresses in chemical deposited vitreous films", <i>J. Appl. Phys.</i> , Vol. 51, No. 8, 1980, pp 4197.
	D360	Silicon-On-Insulator, <i>European Semiconductor</i> , Mar. 1997, pp. 17-18.
	D361	Sioshansi, Piran, "Ion Beam Modification of Materials for Industry," <i>Thin Solid Film</i> , vol. 118, 1984, pp. 61-71.
	D362	Snyman, H. C., "Transmission Electron Microscopy of Extended Crystal Defects in Proton Bombarded and Annealed GaAs", <i>Radiation Effects</i> , 1983, vol. 69, pp. 199-230.
	D363	Snyman, H. C. et al, "Void Formation in Annealed Proton-Bombarded GaAs", 1981, pp. 243-245.
	D364	Stein, Myers and Follstaedt, "Infrared Spectroscopy of chemically bonded hydrogen at voids and defects in silicon", <i>J. Appl. Phys.</i> 73(b6), Mar. 15, 1993, pp. 2755-2764.
	D365	Stephen, D., "Investigation of Lattice Strain in Proton-Irradiated GaP by a Modified Auleytnre Technique" <i>Phys. stat. sol. (a)</i> 87, 1985, pp. 589- 596.
	D366	Sunkara et al., "Bulk synthesis of silicon nanowires using a low-temperature vapor-liquid-solid solution", <i>Applied Physics Letters</i> , Vol. 79, No. 10, September 3, 2001, pp 1546-1548.
	D367	Sze, S.M., <i>VLSI Technology</i> , 2.sup.nd Ed., 1988, pp. 9-10.
	D368	Tan, T. Y. et al., "On Oxygen Precipitation Retardation/Recovery Phenomena, Nucleation Incubation Phenomena and The Exigent-Accommodation-Volume Factor of Precipitation", Proceedings of the 5 <sup>th</sup> International Symposium On Silicon Materials Science and Technology, <i>Semiconductor Silicon 198 Electrochem. Soc.</i> , New Jersey, 1986, pp 864-873.

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
D369	Terada, K. et al., "A New Dram Cell With A Transistor On A Lateral Epitaxial Silicon Layer (Tole Cell)", <i>IEEE Transactions On Electron Device</i> , Vol. 37, No. 9, 1990, pp 2052-2057.	
D370	Theodore, N. David et al., "TFSOI With Improved Oxidation Resistance (To Reduce Isolation Induced Stresses and Leakage)", <i>Motorola Bulletin XP 000691920, Technical Developments</i> , Nov. 1996, pp 158-59.	
D371	Tillman et al., "Zero-Level Packaging for MEMS or MST Devices: The IRS Method", <i>MEMS/Sensors, Advancing Microelectronics</i> , Pages 37-39, November/December 2000.	
D372	Tomisaka et al., "Electroplating Cu Fillings for Through-Vias for Three-Dimensional Chip Stacking" ( <i>Electronic Components and Technology Conference</i> , 2002).	
D373	Tonini, Monelli, Corni, Ottaviani, Frabboni, Canteri, Queirolo, "Hydrogen Interaction with phosphorus ion implanted silicon", <i>Ion Implantation Technology -94</i> , (1995) pp. 801-804.	
D374	Tzeng, J.C., "A Novel Self-Aligned Oxygen (Salox) Implanted SOI Mosfet Device Structure" <i>Nuclear Instruments and Methods in Physics Research B2</i> , 1987, pp. 112-115.	
D375	U.S. Dept. of Energy, "The Fusion Connection: Contributions to Industry, Defense, and Basic Science Resulting From Scientific Advances Made in the Magnetic Fusion Energy Program", <i>Plasma Coating</i> , pp. 6-7, 1985.	
D376	Van de Walle, C. "Structural Identification of Hydrogen and Muonium Centers in Silicon First Principles Calculations of Hyperfine Parameters", <i>Physical Review Letters</i> , Vol. 60, No. 26, 1988, pp 2761-2764.	
D377	Van de Walle, C. "Theoretical Aspects of Hydrogen in Crystalline Semiconductors", <i>Physica B</i> , Holland, Vol. 170, No. 15, 1991, pp 21-32.	
D378	Van de Walle, C. "Theory of Hydrogen Diffusion and Reactions in Crystalline Silicon", <i>Physical Review Letters</i> , Vol. 64, No. 6, 1980, pp 669-672.	
D379	Van de Walle, C. "Theory of Hydrogen Diffusion and Reactions in Crystalline Silicon", <i>Physical Review B</i> , Vol. 39, No. 15, 1989, pp 10 791-10 808, plus diagrams.	
D380	Van Swijgenhoven et al. "Helium Bubble and Blister Formation for Nickel and An AMorphous Fe-Ni-Mo-B Alloy During 5 kev He-+ Irradiation at Temperatures Between 200 K and 600", <i>Nuclear Instruments and Methods</i> , 209/210, 1983, pp. 461-468.	
D381	Veldkamp, W.B. et al., "Binary Optics," <i>Scientific American</i> , 1992, pp. 50-55.	
D382	Venezia et al., "The Role of Implantation Damage in the Production of Silicon-On-Insulator Films By Co-Implantation Of He <sup>+</sup> and H <sup>+</sup> ", <i>Electrochemical Society Proceedings Volume 98-1</i> , 1998 - pp. 1384-1395.	
D383	Weldon et al., "Mechanism Of Silicon Exfoliation Induced by Hydrogen/Hekium Co-implantation", <i>Applied Physics Letters</i> , Vol. 73, No. 25, pp 3721-3723, Dec 21, 1998.	

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449		SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>		FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)		APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)		
D384	Wemple, S.H., "Optical and channeling studies of ion-bombarded GaP", <i>J. Appl. Phys.</i> , vol. 45, No.4, Apr. 1974, pp 1578-1588.		
D385	Whitton, J. L. et al., "The Collection of Ions Implanted In Semiconductors: 1 Saturation Effects", <i>Radiation Effects</i> , Scotland, Vol. 16, 1972, pp 101-105.		
D386	Wiegand, M. et al., "Wafer Bonding of Silicon Wafers Covered With Various Surface Layers", <i>Sensors and Actuators</i> , Elsevier Science B.V., Vol. 86, 2000, pp 91-95.		
D387	Williams J. et al., "Annealing behaviour of high-dose rare-gas implantations into silicon", from Application of Ion Beams to Materials, 1975, Chap. 1, <i>Inst. Phys. Conf. Ser. No. 28</i> , 1976, pp 30-36.		
D388	Wittmaack et al., "High Fluence Retention of Noble Gases Implanted in Silicon" <i>Radiation Effects</i> , vol. 39, 1978, pp. 81-95.		
D389	Wolf, Stanley Ph.D., <i>Silicon Processing for the VLSI Era</i> (vol. 2), Lattice Press, 1990, pp. 66-79.		
D390	Yamaguchi H. et al., "Intelligent Power IC With Partial Soi Structure", <i>Jpn. J. Appl. Phys.</i> , Vol. 34, 1995, pp 864-868.		
D391	Yee et al., "Polysilicon Surface-Modification Technique to Reduce Sticking of Microstructures", <i>Sensors and Actuators A</i> 52, 1996, pp. 145-150.		
D392	Yun, H. et al., "Transfer of Patterned Ion-Cut Silicon Layers", <i>Applied Physics Letters</i> , Vol. 73, No. 19, 1998, pp 2772-2774.		
D393	International Search Report for International Application No. PCT/FR1998/002904, dated April 16, 1999, 2 pages.		
D394	International Search Report for International Application No. PCT/FR2002/003422, dated January 22, 2003, 3 pages.		
D395	International Search Report for International Application No. PCT/FR2003/003256, dated March 19, 2004, 6 pages.		
D396	International Search Report for International Application No. PCT/FR2003/003867, dated May 28, 2004, 3 pages.		
D397	International Search Report for International Application No. PCT/FR2003/003622, dated June 3, 2004, 3 pages.		
D398	International Search Report for International Application No. PCT/FR2004/001858, dated December 28, 2004, 3 pages.		
D399	International Search Report for International Application No. PCT/FR2004/002779, dated April 5, 2005, 3 pages.		
D400	International Search Report for International Application No. PCT/FR2004/002781, dated April 5, 2005, 3 pages.		
D401	International Search Report for International Application No. PCT/FR2004/001565, dated July 6, 2005, 3 pages.		
D402	International Search Report for International Application No. PCT/FR2006/002184, dated January 24, 2007, 2 pages.		

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449		SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>		FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)		APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)		
D403	International Search Report for International Application No. PCT/FR2007/000534, dated November 22, 2007, 3 pages.		
D404	International Search Report for International Application No. PCT/FR2007/002100, dated February 4, 2009, 3 pages.		
D405	International Search Report for International Application No. PCT/FR2008/001427, dated July 1, 2009, 3 pages.		
D406	Office Action from US Application No. 12/063,808, dated April 6, 2010, 9 pages.		
D407	Office Action from US Application No. 12/063,808, dated September 22, 2010, 9 pages.		
D408	Office Action from US Application No. 10/534,199, dated February 19, 2009, 8 pages.		
D409	Office Action from US Application No. 10/534,199, dated August 5, 2009, 10 pages.		
D410	Office Action from US Application No. 10/534,199, dated January 20, 2010, 8 pages.		
D411	Office Action from US Application No. 10/534,199, dated August 4, 2010, 8 pages.		
D412	Office Action from US Application No. 11/480,250, dated May 22, 2008, 10 pages.		
D413	Office Action from US Application No. 11/480,250, dated December 3, 2008, 16 pages.		
D414	Office Action from US Application No. 11/480,250, dated January 26, 2010, 14 pages.		
D415	Office Action from US Application No. 11/480,250, dated August 3, 2010, 15 pages.		
D416	Office Action from US Application No. 12/088,047, dated September 25, 2009, 9 pages.		
D417	Office Action from US Application No. 12/088,047, dated March 10, 2010, 9 pages.		
D418	Office Action from US Application No. 10/561,299, dated March 26, 2008, 9 pages.		
D419	Office Action from US Application No. 10/561,299, dated December 9, 2008, 11 pages.		
D420	Office Action from US Application No. 10/561,299, dated May 11, 2009, 12 pages.		
D421	Office Action from US Application No. 10/561,299, dated November 16, 2009, 11 pages.		
D422	Office Action from US Application No. 10/561,299, dated November 27, 2009, 10 pages.		
D423	Office Action from US Application No. 10/561,299, dated May 11, 2010, 11 pages.		
D424	Office Action from US Application No. 10/565,621, dated May 15, 2007, 13 pages.		
D425	Office Action from US Application No. 10/565,621, dated February 11, 2008, 11 pages.		
D426	Office Action from US Application No. 10/565,621, dated September 12, 2008, 9 pages.		
D427	Office Action from US Application No. 10/565,621, dated March 12, 2009, 6 pages.		
D428	Office Action from US Application No. 10/565,621, dated January 7, 2010, 8 pages.		
D429	Office Action from US Application No. 10/565,621, dated November 23, 2010, 11 pages.		

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
D430	Office Action from US Application No. 12/628,772, dated October 7, 2010, 12 pages.	
D431	Notice of Allowance from US Application No. 12/336,229, dated September 29, 2010, 7 pages.	
D432	Notice of Allowance from US Application No. 12/336,229, dated January 10, 2011, 4 pages.	
D433	Office Action from US Application No. 10/468,223, dated October 5, 2005, 7 pages.	
D434	Office Action from US Application No. 10/468,223, dated May 3, 2006, 11 pages.	
D435	Office Action from US Application No. 10/468,223, dated January 10, 2007, 11 pages.	
D436	Office Action from US Application No. 10/468,223, dated July 20, 2007, 11 pages.	
D437	Office Action from US Application No. 10/468,223, dated February 11, 2008, 11 pages.	
D438	Office Action from US Application No. 10/468,223, dated October 29, 2008, 11 pages.	
D439	Office Action from US Application No. 10/468,223, dated June 25, 2009, 8 pages.	
D440	Notice of Allowance from US Application No. 10/468,223, dated December 28, 2009, 4 pages.	
D441	Office Action from US Application No. 10/474,984, dated September 24, 2004, 6 pages.	
D442	Office Action from US Application No. 10/474,984, dated June 6, 2005, 5 pages.	
D443	Office Action from US Application No. 10/474,984, dated November 16, 2005, 5 pages.	
D444	Office Action from US Application No. 10/474,984, dated May 17, 2006, 5 pages.	
D445	Office Action from US Application No. 10/474,984, dated May 7, 2007, 9 pages.	
D446	Office Action from US Application No. 10/474,984, dated February 6, 2008, 10 pages.	
D447	Office Action from US Application No. 10/474,984, dated October 17, 2008, 11 pages.	
D448	Office Action from US Application No. 10/474,984, dated July 7, 2009, 10 pages.	
D449	Office Action from US Application No. 10/474,984, dated March 11, 2010, 13 pages.	
D450	Notice of Allowance from US Application No. 10/474,984, dated October 28, 2010, 6 pages.	
D451	Office Action from US Application No. 10/540,303, dated December 18, 2007, 6 pages.	
D452	Notice of Allowance from US Application No. 10/540,303, dated October 7, 2008, 9 pages.	
D453	Office Action from US Application No. 11/327,906, dated October 1, 2007, 5 pages.	
D454	Office Action from US Application No. 11/327,906, dated February 11, 2008, 5 pages.	
D455	Notice of Allowance from US Application No. 11/327,906, dated September 15, 2008, 6 pages.	
D456	Office Action from US Application No. 10/975,826, dated September 2, 2009, 24 pages.	

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
	D457	Notice of Allowance from US Application No. 10/975,826, dated April 28, 2010, 8 pages.
	D458	Office Action from US Application No. 10/492,343, dated October 17, 2005, 6 pages.
	D459	Office Action from US Application No. 10/492,343, dated June 6, 2006, 13 pages.
	D460	Office Action from US Application No. 10/492,343, dated November 14, 2006, 13 pages.
	D461	Office Action from US Application No. 10/492,343, dated May 29, 2007, 15 pages.
	D462	Office Action from US Application No. 10/492,343, dated February 7, 2008, 18 pages.
	D463	Office Action from US Application No. 10/492,343, dated August 18, 2008, 12 pages.
	D464	Office Action from US Application No. 10/492,343, dated December 22, 2008, 9 pages.
	D465	Notice of Allowance from US Application No. 10/492,343, dated June 26, 2009, 6 pages.
	D466	Office Action from US Application No. 11/747,733, dated March 16, 2009, 9 pages.
	D467	Office Action from US Application No. 11/747,733, dated March 23, 2010, 5 pages.
	D468	Notice of Allowance from US Application No. 11/747,733, dated September 29, 2010, 8 pages.
	D469	Notice of Allowance from US Application No. 12/293,193, dated October 8, 2009, 10 pages.
	D470	Expert Report of Marcus Weldon, Ph.D. dated November 1, 2000
	D471	Expert Report of Jean-Pierre Colinge dated November 1, 2000.
	D472	Expert Report of Chris Van de Walle, Ph.D. dated November 1, 2000
	D473	Memorandum in Support of Defendant Silicon Genesis Corporation's Motion for Summary Judgment of Invalidity for Lack of Enablement dated March 19, 2001
	D474	Memorandum of Points and Authorities In Support of Soitec's Motion for Summary Judgment on Sigen's Enablement Invalidity Claim (Redacted) dated March 27, 2001
	D475	Soitec's Memorandum of Points and Authorities In Opposition to Silicon Genesis Corporation's Motion for Summary Judgment of Invalidity for Lack of Enablement dated April 11, 2001
	D476	Memorandum in Support of Defendant Silicon Genesis Corporation's Opposition to Soitec's Motion for Summary Judgment on SiGen's Defense of Enablement dated April 20, 2001
	D477	Reply Memorandum in Support of Defendant Silicon Genesis Corporation's Motion for Summary Judgment of Invalidity for Lack of Enablement dated April 30, 2001
	D478	Expert Report of Marcus Weldon, Ph.D. dated August 24, 2001
	D479	Report of Jean-Pierre Colinge in Response to SiGen Enablement and Indefiniteness Expert Reports of August 24, 2001

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
D480	Expert Report of Chris Van de Walle, Ph.D. dated August 24, 2001	
D481	Memorandum and Order re: Summary Judgment [denied] dated February 5, 2002	
D482	Plaintiff's Memorandum in Support of Their Motion for Judgment As a Matter of Law and a New Trial dated May 10, 2002	
D483	Silicon Genesis Corporation's Opposition to Plaintiff's Motion for Judgment as a Matter of Law and a New Trial dated June 17, 2002	
D484	Memorandum of Law in Support of Plaintiff's Motion for Judgment on SiGen's Indefiniteness Defense dated June 20, 2002	
D485	Plaintiff's Reply Memorandum in Support of Their Motion for Judgment as a Matter of Law and a New Trial dated July 18, 2002	
D486	Defendant Silicon Genesis Corporation's Opposition to Soitec's Motion for Judgment Re Indefiniteness and Cross-Motion for Judgment of Indefiniteness dated July 19, 2002	
D487	Plaintiff's Reply in Support of their Motion for Judgment on SiGen's Indefiniteness Defense dated July 25, 2002	
D488	Memorandum and Order re: Post-Trial Motions dated August 23, 2002	
D489	Judgment dated October 21, 2002.	
D490	Brief of Plaintiffs-Appellants Soitec, S.A. and Commissariat a L'Energie Atomique dated January 28, 2003	
D491	Brief for Defendant-Cross Appellant Silicon Genesis Corporation dated March 22, 2003	
D492	Reply Brief of Plaintiffs-Appellants Soitec, S.A. and Commissariat a L'Energie Atomique dated May 5, 2003	
D493	Reply Brief for Defendant-Cross Appellant Silicon Genesis Corporation dated May 19, 2003	
D494	Plaintiff/Appellants Supplemental Authority Letter [dated November 17, 2003].	
D495	Defendant-Cross Appellant's Response To Appellants' Submission Of <i>CFMT, Inc. v. Yieldup Int'l</i> , [dated November 24, 2003].	
D496	Decision from the United States Court of Appeals for the Federal Circuit dated November 26, 2003.	
D497	Combined Petition for Panel Rehearing and for Rehearing En Banc by Plaintiffs-Appellant's Soitec, S.A. and Commissariat A L'Energie Atomique, dated December 10, 2003.	
D498	Order [dated January 7, 2004 denying Appellants' petition for panel rehearing and Appellant's petition for rehearing en banc].	
D499	Judgment Mandate [dated January 14, 2004].	

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
D500	NOTICE of by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique re <u>30</u> MOTION to Dismiss Based upon Fed. R. Civ. P. 12(b)(1) and (6) and Article III of the United States Constitution MOTION to Dismiss Based upon Fed. R. Civ. P. 12(b)(1) and (6) and Article III of the United States Constitution Notice of Withdrawal of Plaintiffs' Partial Motion to Dismiss Counterclaim Counts II, III, IV, V, and VIII (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2009)	
D501	STIPULATION and [Proposed] Order to File an Amended Complaint by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/16/2009)	
D502	NOTICE OF SERVICE of Soitec's Objections and Responses to MEMC's Second Request For Production of Documents and Things Directed To Soitec re <u>46</u> Notice of Service by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. Related document: <u>46</u> Notice of Service filed by MEMC Electronic Materials Inc. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/16/2009)	
D503	First AMENDED COMPLAINT for Patent Infringement against MEMC Electronic Materials Inc.- filed by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Exhibit Exhibit 1, # <u>2</u> Exhibit Exhibit 2, # <u>3</u> Exhibit Exhibit 3, # <u>4</u> Exhibit Exhibit 4, # <u>5</u> Certificate of Service)(Kraft, Denise) (Entered: 07/21/2009)	
D504	ANSWER to Amended Complaint ANSWER to <u>57</u> Amended Complaint, with Under Federal Rule of Civil Procedure 38, MEMC demands a trial by jury on all issues so triable., COUNTERCLAIM against all plaintiffs by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 08/03/2009)	
D505	ANSWER to <u>60</u> Answer to Amended Complaint, Counterclaim,,, COUNTERCLAIM Reply to Defendant's Amended Counterclaims, Counterclaims And Affirmative Defenses against MEMC Electronic Materials Inc. by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/31/2009)	
D506	NOTICE OF SERVICE of MEMC's THIRD SET OF INTERROGATORIES DIRECTED TO S.O.I.TEC SILICON ON INSULATOR TECHNOLOGIES, S.A., SOITEC USA, INC., AND COMMISSARIAT A L'ENERGIE ATOMIQUE by MEMC Electronic Materials Inc. (Rogowski, Patricia) (Entered: 09/01/2009)	

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
D507	ANSWER to <u>68</u> Answer to Counterclaim,,, by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 09/14/2009). Minute Entry for proceedings held before Judge Sue L. Robinson - Discovery Conference held on 9/16/2009. (Court Reporter V. Gunning.) (nmf) (Entered: 09/16/2009)	
D508	MOTION to Bifurcate the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 10/20/2009).  CORRECTING ENTRY: Docket clerk deleted D.I. 78 (opening brief) due to document being filed improperly. Counsel is advised to re-file document using the OPENING BRIEF event code rather than the combined opening and answering brief event code. (lid) (Entered: 10/21/2009)	
D509	OPENING BRIEF in Support re <u>77</u> MOTION to Bifurcate the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order filed by MEMC Electronic Materials Inc..Answering Brief/Response due date per Local Rules is 11/9/2009. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Exhibit B, # <u>3</u> Exhibit C)(Rogowski, Patricia) (Entered: 10/21/2009)	
D510	Cross MOTION to Bifurcate all Collateral Issues - filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 11/09/2009)	
D511	ANSWERING BRIEF in Opposition re <u>85</u> Cross MOTION to Bifurcate all Collateral Issues, <u>77</u> MOTION to Bifurcate the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order filed by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique.Reply Brief due date per Local Rules is 11/20/2009. (Attachments: # <u>1</u> Exhibit, # <u>2</u> Exhibit, # <u>3</u> Exhibit, # <u>4</u> Exhibit, # <u>5</u> Exhibit, # <u>6</u> Exhibit, # <u>7</u> Exhibit, # <u>8</u> Exhibit, # <u>9</u> Exhibit, # <u>10</u> Exhibit, # <u>11</u> Exhibit, # <u>12</u> Declaration, # <u>13</u> Certificate of Service)(Kraft, Denise) (Entered: 11/09/2009)	
D512	REPLY BRIEF re <u>77</u> MOTION to Bifurcate the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Exhibit 2, # <u>3</u> Exhibit 3)(Rogowski, Patricia) (Entered: 11/17/2009)	
D513	ANSWERING BRIEF in Opposition re <u>85</u> Cross MOTION to Bifurcate all Collateral Issues filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 12/3/2009. (Rogowski, Patricia) (Entered: 11/19/2009)	

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
D514	REPLY BRIEF re <u>85</u> Cross MOTION to Bifurcate all Collateral Issues filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit Declaration of Marcus T. Hall in Support of Plaintiffs' Reply Re: Cross-Motion to Bifurcate all Collateral Issues)(Kraft, Denise) (Entered: 12/03/2009)	
D515	NOTICE OF SERVICE of S.O.I.TEC Silicon On Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Production of Three Boxes of Wafer Samples by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 12/08/2009). Set Hearings: Discovery Conference set for 12/21/2009 04:00 PM in Courtroom 6B before Judge Sue L. Robinson. (nmf) (Entered: 12/09/2009).	
D516	MOTION for Leave to File Stipulated Motion for Leave to File a Sur-Reply Brief in Support of MEMC's Motion to Bifurcate - filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1)(Rogowski, Patricia) (Entered: 12/14/2009)	
D517	SUR-REPLY BRIEF re <u>77</u> MOTION to Bifurcate the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order MEMC's SUR-REPLY BRIEF IN SUPPORT OF ITS MOTION TO BIFURCATE THE ISSUES OF WILLFULNESS AND DAMAGES FOR PURPOSES OF DISCOVERY AND TRIAL filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 12/16/2009)	
D518	MOTION for Discovery MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 05/07/2010)	
D519	OPENING BRIEF in Support re <u>141</u> MOTION for Discovery MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 filed by MEMC Electronic Materials Inc.. Answering Brief/Response due date per Local Rules is 5/24/2010. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Exhibit 2, # <u>3</u> Exhibit 3, # <u>4</u> Exhibit 4, # <u>5</u> Exhibit 5, # <u>6</u> Exhibit 6, # <u>7</u> Exhibit 7, # <u>8</u> Exhibit 8, # <u>9</u> Exhibit 9, # <u>10</u> Exhibit 10, # <u>11</u> Exhibit 11, # <u>12</u> Exhibit 12, # <u>13</u> Exhibit 13, # <u>14</u> Exhibit 14, # <u>15</u> Exhibit 15)(Rogowski, Patricia) (Entered: 05/07/2010)	

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
	D520	ANSWERING BRIEF in Opposition re <u>141</u> MOTION for Discovery MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 Plaintiff's Answering Brief in Opposition to Defendant's Motion For the Admission of Expert Testimony of John T. Goolkasian filed by SOITEC Silicon On Insulator Technologies SA. Reply Brief due date per Local Rules is 6/4/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 05/24/2010)
	D521	DECLARATION re <u>145</u> Answering Brief in Opposition,, Declaration of Marcus T. Hall in Support of Plaintiff's Answering Brief in Opposition to Defendant's Motion For the Admission of Expert Testimony of John T. Goolkasian by SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Exhibit B, # <u>3</u> Exhibit C, # <u>4</u> Exhibit D, # <u>5</u> Exhibit E, # <u>6</u> Exhibit F, # <u>7</u> Exhibit G, # <u>8</u> Exhibit H, # <u>9</u> Exhibit I, # <u>10</u> Exhibit J, # <u>11</u> Exhibit K, # <u>12</u> Exhibit L, # <u>13</u> Exhibit M, # <u>14</u> Exhibit N, # <u>15</u> Certificate of Service)(Kraft, Denise) (Entered: 05/24/2010)
	D522	REPLY BRIEF IN SUPPORT OF <u>141</u> MOTION for Discovery MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Exhibit 2, # <u>3</u> Exhibit 3, # <u>4</u> Exhibit 4, # <u>5</u> Exhibit 5, # <u>6</u> Exhibit 6)(Rogowski, Patricia) Modified on 6/4/2010 (lid). (Entered: 06/04/2010)
	D523	STATEMENT re <u>148</u> Stipulation Joint Claim Construction Statement by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/14/2010)
	D524	CLAIM Construction Chart by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/14/2010)
	D525	SUR-REPLY BRIEF re <u>141</u> MOTION for Discovery MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 Surreply by Plaintiffs to Motion by Defendant For The Admission of Expert Testimony of John T. Goolkasian filed by SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/15/2010)
	D526	DECLARATION re <u>157</u> Sur-Reply Brief, Declaration of Marcus T. Hall in Support of Surreply by Plaintiffs to Motion by Defendant For The Admission of Expert Testimony of John T. Goolkasian by SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Exhibit B, # <u>3</u> Exhibit C, # <u>4</u> Exhibit D, # <u>5</u> Certificate of Service)(Kraft, Denise) (Entered: 06/15/2010)
EXAMINER		DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
D527	CLAIM CONSTRUCTION OPENING BRIEF filed by MEMC Electronic Materials Inc.. (Attachments: # 1 Appendix DA0001-DA0006, # 2 Appendix DA0007-DA0032, # 3 Appendix DA0033-DA0072, # 4 Appendix DA0073-DA0112, # 5 Appendix DA0113-DA0152, # 6 Appendix DA0153-DA0192, # 7 Appendix DA0193-DA0232, # 8 Appendix DA0233-DA0272, # 9 Appendix DA0273-DA0312, # 10 Appendix DA0313-DA0352, # 11 Appendix DA0353-DA0392, # 12 Appendix DA0393-DA0432, # 13 Appendix DA0433-DA0472, # 14 Appendix DA0473-DA0512, # 15 Appendix DA0513-DA0521, # 16 Appendix DA0522-DA0545, # 17 Appendix SEALED - DA0546-DA0551, # 18 Appendix DA0552-DA0563, # 19 Appendix SEALED - DA0564-DA0566, # 20 Appendix DA0567-DA0573, # 21 Appendix SEALED - DA0574-DA0599, # 22 Appendix DA0600-DA0604, # 23 Appendix DA0605-DA0609, # 24 Appendix DA0610-DA0625, # 25 Appendix DA0626-0634, # 26 Appendix DA0635, # 27 Appendix DA0636-DA0652, # 28 Appendix SEALED - DA0653-DA0657, # 29 Appendix DA0658-DA0667, # 30 Appendix DA0668-DA0670, # 31 Appendix DA0671-DA0678, # 32 Appendix DA0679-DA0687, # 33 Appendix DA0688-DA0696, # 34 Appendix SEALED - DA0697-DA0705, # 35 Appendix SEALED - DA0706-DA0711, # 36 Appendix SEALED - DA0712-DA0714, # 37 Appendix DA0715-DA0717, # 38 Appendix DA0718-DA0719, # 39 Appendix DA0720-DA0722, # 40 Appendix DA0723-DA0732, # 41 Appendix DA0733-DA0740, # 42 Appendix DA0741-DA0749, # 43 Appendix DA0750-DA0769, # 44 Appendix DA0770-DA0781)(Rogowski, Patricia) (Entered: 06/25/2010)	
D528	CLAIM CONSTRUCTION OPENING BRIEF Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 06/25/2010)	
D529	DECLARATION re <u>168</u> Claim Construction Opening Brief, Declaration of Marcus T. Hall in Support of Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 06/25/2010)	

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
D530	APPENDIX re <u>167</u> Claim Construction Opening Brief, , , , , by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix DA-0001 - DA-0006, # <u>2</u> Appendix DA-0007 - DA-0032, # <u>3</u> Appendix DA-0033 - DA-0072, # <u>4</u> Appendix DA-0073 - DA-0112, # <u>5</u> Appendix DA-0113 - DA-0152, # <u>6</u> Appendix DA-0153 - DA-0192, # <u>7</u> Appendix DA-0193 - DA-0232, # <u>8</u> Appendix DA-0233 - DA-0272, # <u>9</u> Appendix DA-0273 - DA-0312, # <u>10</u> Appendix DA-0313 - DA-0352, # <u>11</u> Appendix DA-0353 - DA-0392, # <u>12</u> Appendix DA-0393 - DA-0432, # <u>13</u> Appendix DA-0433 - DA-0472, # <u>14</u> Appendix DA-0473 - DA-0512, # <u>15</u> Appendix DA-0513 - DA-0521)(Rogowski, Patricia) (Entered: 06/28/2010)	
D531	REDACTED VERSION of <u>175</u> Appendix by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix DA0522-DA0545, # <u>2</u> Appendix DA0546-DA0551, # <u>3</u> Appendix DA0552-DA0563, # <u>4</u> Appendix DA0564-DA0566, # <u>5</u> Appendix DA0567-DA0573, # <u>6</u> Appendix DA0574-DA0599, # <u>7</u> Appendix DA0600-DA0604, # <u>8</u> Appendix DA0605-DA0609, # <u>9</u> Appendix DA0610-DA0625, # <u>10</u> Appendix DA0626-DA0634, # <u>11</u> Appendix DA0635, # <u>12</u> Appendix DA0636-DA0652, # <u>13</u> Appendix DA0653-DA0657, # <u>14</u> Appendix DA0658-DA0667, # <u>15</u> Appendix DA0668-DA0670, # <u>16</u> Appendix DA0671-DA0678, # <u>17</u> Appendix DA0679-DA0687, # <u>18</u> Appendix DA0688-DA0696, # <u>19</u> Appendix DA0697-DA0705, # <u>20</u> Appendix DA0706-DA-0711, # <u>21</u> Appendix DA0712-DA0714, # <u>22</u> Appendix DA0715-DA0717, # <u>23</u> Appendix DA0718-DA0719, # <u>24</u> Appendix DA0720-DA0722, # <u>25</u> Appendix DA0723-DA0732, # <u>26</u> Appendix DA0733-DA0740, # <u>27</u> Appendix DA0741-DA0749, # <u>28</u> Appendix DA0750-DA0769, # <u>29</u> Appendix DA0770-DA0781, # <u>30</u> Certificate of Service)(Rogowski, Patricia) (Entered: 06/28/2010)	
D532	NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (1) Vol. I - JA0001 to JA0533. APPENDIX VOL I. re <u>173</u> Notice of Filing Paper Documents(OVERSIZED DOCUMENT, ITEM ON FILE IN THE CLERKS OFFICE). (lid) (Entered: 06/28/2010).	
D533	NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (2) Vol. II - JA0534 to JA0930. APPENDIX VOL II. re <u>173</u> Notice of Filing Paper Documents(OVERSIZED DOCUMENT, ITEM ON FILE IN THE CLERKS OFFICE). (lid) (Entered: 06/28/2010).	
D534	NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (3) Vol. III – JA0931 to JA1502. APPENDIX VOL III. re <u>173</u> Notice of Filing Paper Documents(OVERSIZED DOCUMENT, ITEM ON FILE IN THE CLERKS OFFICE) (lid) (Entered: 06/28/2010) (2 parts).	

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
D535	NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (4) Vol. IV – JA1503 to JA1510. APPENDIX VOL IV. re <u>173</u> Notice of Filing Paper Documents, (OVERSIZED DOCUMENT, ITEM ON FILE IN THE CLERKS OFFICE) (lid) (Entered: 06/28/2010).	
D536	NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (5) Vol. V – JA1511 to JA2089 (2 parts).	
D537	Vol. VI - JA2090 to JA2557. Original document(s) to be filed with the Clerk's Office. Notice filed by Denise Seastone Kraft on behalf of Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/25/2010).	
D538	MOTION in Limine SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony - filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)	
D539	MOTION for Partial Summary Judgment of Invalidity of the Asserted Aspar Patent Claims - filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/02/2010)	
D540	OPENING BRIEF in Support re <u>186</u> MOTION in Limine SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA.Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)	
D541	OPENING BRIEF in Support re <u>187</u> MOTION for Partial Summary Judgment of Invalidity of the Asserted Aspar Patent Claims filed by MEMC Electronic Materials Inc..Answering Brief/Response due date per Local Rules is 7/19/2010. (Rogowski, Patricia) (Entered: 07/02/2010)	

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
	D542	APPENDIX re <u>186</u> MOTION in Limine SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony Plaintiffs' Omnibus Appendix to Daubert Motion and Motions For Partial Summary Judgment Filed on July 2, 2010 by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Appendix Vol. II of XIX, # <u>2</u> Appendix Vol. III of XIX, # <u>3</u> Appendix Vol. IV of XIX, # <u>4</u> Appendix Vol. V of XIX, # <u>5</u> Appendix Vol. VII of XIX, # <u>6</u> Appendix Vol. IX of XIX, # <u>7</u> Appendix Vol. XI of XIX, # <u>8</u> Appendix Vol. XII of XIX, # <u>9</u> Appendix Vol. XIII of XIX, # <u>10</u> Appendix Vol. XIV of XIX, # <u>11</u> Appendix Vol. XV of XIX, # <u>12</u> Appendix Vol. XVI of XIX, # <u>13</u> Appendix Vol. XVIII of XIX, # <u>14</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
	D543	MOTION for Summary Judgment of Non-Infringement - filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/02/2010)
	D544	MOTION for Partial Summary Judgment SOITEC/CEA Parties Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement - filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
	D545	OPENING BRIEF in Support re <u>202</u> MOTION for Partial Summary Judgment SOITEC/CEA Parties Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
	D546	MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid - filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
	D547	OPENING BRIEF in Support re <u>204</u> MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
	D548	MOTION for Partial Summary Judgment SOITEC/CEA Parties' Motion For Partial Summary Judgment That The Aspar Patents Are Not Invalid For Inequitable Conduct - filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
	D549	OPENING BRIEF in Support re <u>206</u> MOTION for Partial Summary Judgment SOITEC/CEA Parties' Motion For Partial Summary Judgment That The Aspar Patents Are Not Invalid For Inequitable Conduct filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc..Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
	D550	MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Bruel Patent Does Not Anticipate The Aspar Patents - filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
	D551	OPENING BRIEF in Support re <u>208</u> MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Bruel Patent Does Not Anticipate The Aspar Patents filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA.Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
	D552	MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement - filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
	D553	OPENING BRIEF in Support re <u>210</u> MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc..Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
	D554	MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art - filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
	D555	MOTION for Partial Summary Judgment That the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents - filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Reed, John) (Entered: 07/02/2010)
	D556	OPENING BRIEF in Support re <u>212</u> MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc..Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
	D557	OPENING BRIEF in Support re <u>213</u> MOTION for Partial Summary Judgment That the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents filed by SOITEC Silicon On Insulator Technologies SA.Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Reed, John) (Entered: 07/02/2010)
	D558	REDACTED VERSION of <u>200</u> Opening Brief in Support, by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/07/2010)

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)		
APPLICANT(S): Nguyet-Phuong Nguyen et al.		

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
D559	REDACTED VERSION of <u>201</u> Appendix by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix MA0001 - MA0004, # <u>2</u> Appendix MA0005 - MA0010, # <u>3</u> Appendix MA0011 - MA0016, # <u>4</u> Appendix MA0017 - MA0020, # <u>5</u> Appendix MA0021 - MA0029, # <u>6</u> Appendix MA0030 - MA0045, # <u>7</u> Appendix MA0046 - MA0052, # <u>8</u> Appendix MA0053 - MA0078, # <u>9</u> Appendix MA0079 - MA0092, # <u>10</u> Appendix MA0093 - MA0129, # <u>11</u> Appendix MA0130 - MA0148, # <u>12</u> Appendix MA0149 - MA0160, # <u>13</u> Appendix MA0161 - MA0163, # <u>14</u> Appendix MA0164 - MA0167, # <u>15</u> Appendix MA0168 - MA0172, # <u>16</u> Appendix MA0173 - MA0183, # <u>17</u> Appendix MA0184 - MA0196, # <u>18</u> Appendix MA0197 - MA0207, # <u>19</u> Appendix MA0208 - MA0241, # <u>20</u> Appendix MA0242 - MA0245, # <u>21</u> Appendix MA0246 - MA0249, # <u>22</u> Appendix MA0250 - MA0252, # <u>23</u> Appendix MA0253 - MA0265, # <u>24</u> Appendix MA0266 - MA0281, # <u>25</u> Appendix MA0282 - MA0312, # <u>26</u> Appendix MA0313 - MA0359, # <u>27</u> Appendix MA0360 - MA0365, # <u>28</u> Appendix MA0366, # <u>29</u> Appendix MA0367 - MA0400, # <u>30</u> Appendix MA0401 - MA0474, # <u>31</u> Appendix MA0475 - MA0483, # <u>32</u> Certificate)(Rogowski, Patricia) (Entered: 07/07/2010)	
D560	REDACTED VERSION of <u>190</u> Appendix by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix MA0484 - MA0489, # <u>2</u> Appendix MA0490 - MA0515, # <u>3</u> Appendix MA0516 - MA0534, # <u>4</u> Appendix MA0535 - MA0541, # <u>5</u> Appendix MA0542 - MA0550, # <u>6</u> Appendix MA0551 - MA0561, # <u>7</u> Appendix MA0562 - MA0564, # <u>8</u> Appendix MA0565 - MA0569, # <u>9</u> Appendix MA0570 - MA0574, # <u>10</u> Appendix MA0575 - MA0576, # <u>11</u> Appendix MA0577 - MA0601, # <u>12</u> Appendix MA0602 - MA0603, # <u>13</u> Appendix MA0604 - MA0605, # <u>14</u> Appendix MA0606 - MA0609, # <u>15</u> Appendix MA0610 - MA0612, # <u>16</u> Appendix MA0613 - MA0625, # <u>17</u> Appendix MA0626 - MA0628, # <u>18</u> Appendix MA0629 - MA0630, # <u>19</u> Appendix MA0631 - MA0653, # <u>20</u> Appendix MA0654 - MA0685, # <u>21</u> Appendix MA0686 - MA0701, # <u>22</u> Appendix MA0702 - MA0732, # <u>23</u> Appendix MA0733 - MA0742, # <u>24</u> Appendix MA0743 - MA0750, # <u>25</u> Appendix MA0751 - MA0766, # <u>26</u> Appendix MA0767 - MA0772, # <u>27</u> Appendix MA0773 - MA0780, # <u>28</u> Appendix MA0781 - MA0807, # <u>29</u> Appendix MA0808 - MA0824, # <u>30</u> Appendix MA0825 - MA0831.1, # <u>31</u> Appendix MA0832 - MA0838, # <u>32</u> Appendix MA0839 - MA0844, # <u>33</u> Appendix MA0845 - MA0858, # <u>34</u> Appendix MA0859 - MA0868, # <u>35</u> Appendix MA0869 - MA0877, # <u>36</u> Appendix MA0878 - MA0884, # <u>37</u> Appendix MA0885 - MA0887, # <u>38</u> Appendix MA0888 - MA0891, # <u>39</u> Appendix MA0892 - MA0909, # <u>40</u> Appendix MA0910 - MA0931, # <u>41</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/07/2010)	
D561	REDACTED VERSION of <u>198</u> Opening Brief in Support,, SOITEC/CEA Parties' Opening Brief In Support Of Motion For Summary Judgment: Non-Infringement by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/08/2010)	

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449		SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>		FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)		APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)		
	D562	REDACTED VERSION of <u>197</u> SEALED MOTION for Summary Judgment SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement (FILED UNDER SEAL)SEALED MOTION for Summary Judgment SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement (FILED UNDER SEAL) SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/08/2010)	
	D563	REDACTED VERSION of <u>192</u> Appendix, Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume VI of XIX by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)	
	D564	REDACTED VERSION of <u>193</u> Appendix, Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume VIII of XIX by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)	
	D565	REDACTED VERSION of <u>194</u> Appendix, Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume X of XIX by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)	
	D566	REDACTED VERSION of <u>195</u> Appendix, Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume XVII of XIX by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)	
	D567	REDACTED VERSION of <u>196</u> Appendix, Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume XIX of XIX by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)	
	D568	CLAIM CONSTRUCTION ANSWERING BRIEF re <u>168</u> Claim Construction Opening Brief, filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/09/2010)	
	D569	APPENDIX re <u>228</u> Claim Construction Answering Brief by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix DA0782_DA0783, # <u>2</u> Appendix DA0784 - DA0785, # <u>3</u> Appendix DA0786, # <u>4</u> Appendix DA0787 - DA0810, # <u>5</u> Appendix DA0811 - DA0834, # <u>6</u> Appendix DA0835 - DA0845, # <u>7</u> Appendix DA0846 - DA0855, # <u>8</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/09/2010)	

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
	D570	CLAIM CONSTRUCTION ANSWERING BRIEF re <u>168</u> Claim Construction Opening Brief, <u>228</u> Claim Construction Answering Brief Plaintiffs S.O.I.TEC On Insulator Technologies, S.A. And Commissariat A Energie Atomique's Answering Claim Construction Brief filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/09/2010)
	D571	APPENDIX re <u>230</u> Claim Construction Answering Brief, Appendix to Plaintiffs S.O.I.TEC On Insulator Technologies, S.A. And Commissariat A Energie Atomique's Answering Claim Construction Brief by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Appendix PA-0001 - PA-0050, # <u>2</u> Appendix PA-0051 - PA-0083, # <u>3</u> Certificate of Service)(Kraft, Denise) (Entered: 07/09/2010)
	D572	REDACTED VERSION of <u>183</u> Appendix, Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs Volume IV of VI by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/12/2010)
	D573	REDACTED VERSION of <u>170</u> Exhibit to a Document, Exhibit A to Declaration of Marcus T. Hall in Support of Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/12/2010)
	D574	REDACTED VERSION of <u>171</u> Exhibit to a Document, Exhibit B to Declaration of Marcus T. Hall in Support of Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/12/2010)
	D575	REDACTED VERSION of <u>172</u> Exhibit to a Document, Exhibit C to Declaration of Marcus T. Hall in Support of Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/12/2010)
	D576	ANSWERING BRIEF in Opposition re <u>186</u> MOTION in Limine SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
D577	ANSWERING BRIEF in Opposition re <u>208</u> MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Bruel Patent Does Not Anticipate The Aspar Patents filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)	
D578	ANSWERING BRIEF in Opposition re <u>202</u> MOTION for Partial Summary Judgment SOITEC/CEA Parties Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)	
D579	ANSWERING BRIEF in Opposition re <u>204</u> MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)	
D580	ANSWERING BRIEF in Opposition re <u>210</u> MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)	
D581	ANSWERING BRIEF in Opposition re <u>212</u> MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)	
D582	APPENDIX re <u>247</u> Answering Brief in Opposition,, Appendix To Plaintiffs' Answering Brief In Opposition To Defendant's Motion For Partial Summary Judgment Of Invalidity Of The Asserted Aspar Claims (PA-1103 - PA-1156) by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit PA-1103 - PA-1109 - FILED UNDER SEAL, # <u>2</u> Exhibit PA-1110 - PA-1118 - FILED UNDER SEAL, # <u>3</u> Exhibit PA-1119 - PA-1130 - FILED UNDER SEAL, # <u>4</u> Exhibit PA-1131 - PA-1143 - FILED UNDER SEAL, # <u>5</u> Exhibit PA-1144 - PA-1156, # <u>6</u> Certificate of Service)(Kraft, Denise) (Entered: 07/19/2010)	
D583	APPENDIX re <u>250</u> Answering Brief in Opposition, Appendix to Plaintiffs' Answering Brief in Opposition to Defendant's Motion For Summary Judgment of Non-Infringement by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit PA-1190 - PA-1191, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/19/2010)	

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
	D584	REDACTED VERSION of <u>241</u> Answering Brief in Opposition, to Plaintiffs' Motion for Partial Summary Judgment that the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 07/26/2010)
	D585	REDACTED VERSION of <u>249</u> Answering Brief in Opposition, to Plaintiffs' Motion for Summary Judgment on the Infringement of U.S. Patent No. 5,834,812 by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 07/26/2010)
	D586	REDACTED VERSION of <u>253</u> Answering Brief in Opposition, to Plaintiffs' Motion for Partial Summary Judgment that the Aspar Patents Are Not Invalid for Inequitable Conduct by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 07/26/2010)
	D587	REDACTED VERSION of <u>240</u> Appendix by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix MA0932 - MA0985, # <u>2</u> Appendix MA0986 - MA1039.22, # <u>3</u> Appendix MA1040 - MA1144, # <u>4</u> Appendix MA1145 - MA1200, # <u>5</u> Appendix MA1201 - MA1265, # <u>6</u> Appendix MA1265.1 - MA1338, # <u>7</u> Appendix MA1339 - MA1547, # <u>8</u> Appendix MA1548 - MA1627, # <u>9</u> Appendix MA1628 - MA1693, # <u>10</u> Appendix MA1694 - MA1953, # <u>11</u> Appendix MA1954 - MA2127, # <u>12</u> Appendix MA2128 - MA2206, # <u>13</u> Appendix MA2207 - MA2253, # <u>14</u> Appendix MA2254 - MA2273, # <u>15</u> Appendix MA2274 - MA2333, # <u>16</u> Appendix MA2334 - MA2337, # <u>17</u> Appendix MA2338 - MA2342, # <u>18</u> Appendix MA2343 - MA2346, # <u>19</u> Appendix MA2347 - MA2351, # <u>20</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/26/2010) (2 parts).
	D588	REDACTED VERSION of <u>261</u> Answering Brief in Opposition, to Plaintiffs' Motion for Partial Summary Judgment that the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents (CORRECTED VERSION OF D.I. 241) by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 07/26/2010)
	D589	REDACTED VERSION of <u>250</u> Answering Brief in Opposition, to Soitec's Brief in Opposition to Defendant's Motion For Summary Judgment of Non-Infringement by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/26/2010)
	D590	REDACTED VERSION of <u>247</u> Answering Brief in Opposition,, to Plaintiffs' Answering Brief In Opposition To Defendant's Motion For Partial Summary Judgment Of In validity Of The Asserted Aspar Claims by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/26/2010)

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
D591	REDACTED VERSION of <u>254</u> Appendix,, to Appendix To Plaintiffs' Answering Brief In Opposition To Defendant's Motion For Partial Summary Judgment Of Invalidity Of The Asserted Aspar Claims (PA-1103 - PA-1143 by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/26/2010)	
D592	REDACTED VERSION of <u>251</u> Appendix,, to Appendix to Plaintiffs' Answering Brief in Opposition to Defendant's Motion For Summary Judgment of Non-Infringement by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/26/2010)	
D593	REPLY BRIEF re <u>204</u> MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid Reply Brief in Support of Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)	
D594	DECLARATION re <u>268</u> Reply Brief, Declaration of Marcus T. Hall in Support of Reply Brief in Support of Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)	
D595	APPENDIX re <u>268</u> Reply Brief, Omnibus Appendix to Plaintiffs' Reply Briefs in Support of Plaintiffs' Daubert Motion and Motions For Partial Summary Judgment (PA-1192 - PA-1261) by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit PA-1199 - PA-1204, # <u>2</u> Exhibit PA-1205 - PA-1206, # <u>3</u> Exhibit PA-1206.1, # <u>4</u> Exhibit PA-1231 - PA-1237, # <u>5</u> Exhibit PA-1238 - PA-1245, # <u>6</u> Exhibit PA-1246 - PA-1257, # <u>7</u> Exhibit PA-1258 - PA-1261, # <u>8</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)	
D596	REPLY BRIEF re <u>210</u> MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement Reply Brief in Support of SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)	

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
	D597	REPLY BRIEF re <u>212</u> MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art Reply Brief in Support of SOITEC's Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Exhibit B, # <u>3</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)
	D598	REPLY BRIEF re <u>202</u> MOTION for Partial Summary Judgment SOITEC/CEA Parties Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement Reply Brief in Support of SOITEC/CEA Parties' Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)
	D599	REDACTED VERSION of <u>269</u> Appendix, TO REPLY BRIEF IN SUPPORT OF MEMC's MOTION FOR PARTIAL SUMMARY JUDGMENT OF INVALIDITY OF THE ASSERTED ASPAR PATENT CLAIMS by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix Table of Contents, # <u>2</u> Appendix MA2453_MA2479, # <u>3</u> Certificate of Service)(Rogowski, Patricia) (Entered: 08/03/2010)
	D600	REDACTED VERSION of <u>273</u> Appendix REPLY BRIEF IN SUPPORT OF MEMC's MOTION FOR SUMMARY JUDGMENT OF NON-INFRINGEMENT by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix Table of Contents, # <u>2</u> Appendix MA2352 - MA2361, # <u>3</u> Appendix MA2362 - MA2371, # <u>4</u> Appendix MA2372 - MA2381, # <u>5</u> Appendix MA2382 - MA2391, # <u>6</u> Appendix MA2392 - MA2399, # <u>7</u> Appendix MA2400 - MA2404, # <u>8</u> Appendix MA2405 - MA2422, # <u>9</u> Appendix MA2423 - MA2425, # <u>10</u> Appendix MA2426 - MA2427, # <u>11</u> Appendix MA2428 - MA2430, # <u>12</u> Appendix MA2431 - MA2440, # <u>13</u> Appendix MA2441 - MA2448, # <u>14</u> Appendix MA2449 - MA2452, # <u>15</u> Appendix MA2452.1 - MA2452.9, # <u>16</u> Certificate of Service)(Rogowski, Patricia) (Entered: 08/03/2010)
	D601	REDACTED VERSION of <u>267</u> Reply Brief IN SUPPORT OF MEMC's MOTION FOR PARTIAL SUMMARY JUDGMENT OF INVALIDITY OF THE ASSERTED ASPAR PATENT CLAIMS by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 08/03/2010)
	D602	REDACTED VERSION of <u>271</u> Reply Brief IN SUPPORT OF MEMC's MOTION FOR SUMMARY JUDGMENT OF NON-INFRINGEMENT by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 08/03/2010)

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
	D603	REDACTED VERSION of <u>274</u> Appendix,, Omnibus Appendix to Plaintiffs' Reply Briefs in Support of Plaintiffs' Daubert Motion and Motions For Partial Summary Judgment (PA-1192 - PA-1198 and PA-1207 - PA-1230 Filed Under Seal) by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 08/06/2010)
	D604	REDACTED VERSION of <u>277</u> Reply Brief, in Support of SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/06/2010)
	D605	REDACTED VERSION of <u>278</u> Reply Brief,, in Support of SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement (Filed Under Seal) by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/06/2010)
	D606	REDACTED VERSION of <u>279</u> Reply Brief,, in Support of Plaintiffs' Motion for Partial Summary Judgment That the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents (Filed Under Seal) by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/06/2010)
	D607	REDACTED VERSION of <u>281</u> Reply Brief, in Support of Plaintiffs' Motion For Partial Summary Judgment That The Bruel Patent Does Not Anticipate The Aspar Patents (Filed Under Seal) by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/06/2010)
	D608	REDACTED VERSION of <u>282</u> Reply Brief,, in Support of SOITEC/CEA Parties' Motion For Partial Summary Judgment That The Aspar Patents Are Not Invalid For Inequitable Conduct (Filed Under Seal) by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/06/2010)
	D609	NOTICE OF SERVICE of CD of documents MEMC0782194-MEMC0782500 and FH-1 0001 - FH-8 0067 by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 09/16/2010)
	D610	REDACTED VERSION of <u>301</u> SEALED MOTION for Reconsideration Request to Modify Protective Order by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 09/24/2010)

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
D611	REDACTED VERSION of <u>302</u> Declaration, of Michael L. Brody in Support of Motion to Reconsider Request to Modify Protective Order by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 09/24/2010)	
D612	REDACTED VERSION of <u>303</u> Exhibit to a Document Exhibit A to Michael L. Brody in Support of Motion to Reconsider Request to Modify Protective Order by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 09/24/2010)	
D613	REDACTED VERSION of <u>304</u> Exhibit to a Document Exhibit B to Michael L. Brody in Support of Motion to Reconsider Request to Modify Protective Order by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 09/24/2010)	
D614	REDACTED VERSION of <u>305</u> Exhibit to a Document Exhibit C to Michael L. Brody in Support of Motion to Reconsider Request to Modify Protective Order by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 09/24/2010)	
D615	REDACTED VERSION of <u>306</u> Exhibit to a Document Exhibit D to Michael L. Brody in Support of Motion to Reconsider Request to Modify Protective Order by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 09/24/2010)	
D616	Proposed Pretrial Order [Proposed] Joint Pretrial Order (FILED UNDER SEAL) by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit 1 (Sealed), # <u>2</u> Exhibit 2A (Sealed), # <u>3</u> Exhibit 2B (Sealed), # <u>4</u> Exhibit 3A (Sealed), # <u>5</u> Exhibit 3B (Sealed), # <u>6</u> Exhibit 4A (Sealed), # <u>7</u> Exhibit 4B (Sealed), # <u>8</u> Exhibit 4C (Sealed), # <u>9</u> Exhibit 5A (Sealed), # <u>10</u> Exhibit 5B (Sealed), # <u>11</u> Exhibit 6A (Sealed), # <u>12</u> Exhibit 6B (Sealed), # <u>13</u> Exhibit 7A (Sealed), # <u>14</u> Exhibit 7B (Sealed), # <u>15</u> Certificate of Service)(Kraft, Denise) (Entered: 10/07/2010)	
D617	Proposed Voir Dire by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 10/08/2010)	
D618	VERDICT SHEET by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 10/08/2010)	
D619	Proposed Voir Dire by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 10/08/2010)	

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
D620	VERDICT SHEET by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 10/08/2010)	
D621	Proposed Jury Instructions by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 10/08/2010)	
D622	Proposed Jury Instructions by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 10/08/2010)	
D623	REDACTED VERSION of <u>315</u> Proposed Pretrial Order,, Redacted Version of [Proposed] Joint Pretrial Order by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Exhibit 2A, # <u>3</u> Exhibit 2B, # <u>4</u> Exhibit 3A, # <u>5</u> Exhibit 3B, # <u>6</u> Exhibit 4A, # <u>7</u> Exhibit 4B, # <u>8</u> Exhibit 4C, # <u>9</u> Exhibit 5A, # <u>10</u> Exhibit 5B, # <u>11</u> Exhibit 6A, # <u>12</u> Exhibit 6B, # <u>13</u> Exhibit 7A, # <u>14</u> Exhibit 7B, # <u>15</u> Certificate of Service)(Kraft, Denise) (Entered: 10/13/2010)	
D624	MEMORANDUM OPINION. Signed by Judge Sue L. Robinson on 10/13/2010. (nmf) (Entered: 10/13/2010)	
D625	ORDER denying <u>141</u> Motion for Discovery; denying <u>186</u> Motion in Limine; granting in part and denying in part <u>187</u> Motion for Partial Summary Judgment; granting <u>197</u> Motion for Summary Judgment ; granting <u>199</u> Motion for Summary Judgment ; granting <u>202</u> Motion for Partial Summary Judgment; denying <u>204</u> Motion for Partial Summary Judgment; denying <u>206</u> Motion for Partial Summary Judgment; granting in part and denying in part <u>208</u> Motion for Partial Summary Judgment; denying <u>210</u> Motion for Partial Summary Judgment; denying <u>212</u> Motion for Partial Summary Judgment; granting in part and denying in part <u>213</u> Motion for Partial Summary Judgment. Signed by Judge Sue L. Robinson on 10/13/2010. (nmf) (Entered: 10/13/2010)	
D626	MEMORANDUM ORDER re: claim construction. Signed by Judge Sue L. Robinson on 10/13/2010. (nmf) (Entered: 10/13/2010) ORAL ORDER by Judge Sue L. Robinson on 10/14/2010 that the responses to the issues raised in the exhibits to the joint pre-trial order are to be stricken from the record. (These filings, formerly D.I. Nos. 318 and 323 have been deleted from the docket.) (nmf) (Entered: 10/14/2010)	

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
	D627	AMENDED ORDER denying <u>141</u> Motion for Discovery; denying <u>186</u> Motion in Limine; granting in part and denying in part <u>187</u> Motion for Partial Summary Judgment; granting <u>197</u> Motion for Summary Judgment ; granting <u>199</u> Motion for Summary Judgment ; granting <u>202</u> Motion for Partial Summary Judgment; denying <u>204</u> Motion for Partial Summary Judgment; denying <u>206</u> Motion for Partial Summary Judgment; granting in part and denying in part <u>208</u> Motion for Partial Summary Judgment; denying <u>210</u> Motion for Partial Summary Judgment; denying <u>212</u> Motion for Partial Summary Judgment; *granting* <u>213</u> Motion for Partial Summary Judgment. Signed by Judge Sue L. Robinson on 10/14/2010. (nmf) (Entered: 10/14/2010) Minute Entry for proceedings held before Judge Sue L. Robinson - Final Pretrial Conference held on 10/14/2010. (Court Reporter V. Gunning.) (nmf) (Entered: 10/15/2010) SO ORDERED, re <u>315</u> Proposed Pretrial Order. Signed by Judge Sue L. Robinson on 10/14/2010. (nmf) (Entered: 10/15/2010)
	D628	MOTION for Reargument re <u>327</u> Memorandum and Order - Reargument of Claim Construction of One Claim Term of U.S. Patent 6,809,009 - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 10/18/2010)
	D629	SECOND AMENDED ORDER re: <u>325</u> denying <u>141</u> Motion for Discovery; denying <u>186</u> Motion in Limine; granting in part and denying in part <u>187</u> Motion for Partial Summary Judgment; granting <u>197</u> Motion for Summary Judgment ; granting <u>199</u> Motion for Summary Judgment **with respect to the '484 patent and with respect to its current process, and denied in other respects; granting <u>202</u> Motion for Partial Summary Judgment; denying <u>204</u> Motion for Partial Summary Judgment; denying <u>206</u> Motion for Partial Summary Judgment; granting in part and denying in part <u>208</u> Motion for Partial Summary Judgment; denying <u>210</u> Motion for Partial Summary Judgment; denying <u>212</u> Motion for Partial Summary Judgment; granting <u>213</u> Motion for Partial Summary Judgment. Signed by Judge Sue L. Robinson on 10/19/2010. (nmf) (Entered: 10/19/2010)
	D630	MEMORANDUM ORDER granting <u>329</u> MOTION for Reargument re <u>327</u> Memorandum and Order - Reargument of Claim Construction of One Claim Term of U.S. Patent 6,809,009. Signed by Judge Sue L. Robinson on 10/19/2010. (nmf) (Entered: 10/19/2010)
	D631	STIPULATION MEMC's Declaratory Judgment counterclaim asserting invalidity of United States Reissued Patent No. 39,484 in Civil Action No. 1:08-292-SLR is dismissed without prejudice by Commissariat a L'energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (nmf, ). (Entered: 10/21/2010)

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
	D632	STIPULATION of Fact re <u>331</u> Memorandum and Order, <u>327</u> Memorandum and Order, <u>325</u> Memorandum Opinion by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 10/21/2010)
	D633	Letter to The Honorable Sue L. Robinson from Denise Seastone Kraft regarding Mutually agreed upon narrowing of the issues for trial - re <u>333</u> Stipulation, <u>332</u> Stipulation,.. (Kraft, Denise) (Entered: 10/21/2010) CORRECTING ENTRY: The pdf of D.I. <u>332</u> has been replaced with the correct pdf of the stipulation per request of filer. (nmf) (Entered: 10/22/2010) SO ORDERED, re <u>333</u> Stipulation filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a L'Energie Atomique, <u>332</u> Stipulation, filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a L'Energie Atomique. Signed by Judge Sue L. Robinson on 10/22/2010. (nmf) (Entered: 10/22/2010)
	D634	Voir Dire Questions. Read in Open Court 10/25/2010.(nmf) (Entered: 10/25/2010)
	D635	Preliminary Jury Instructions. Read in Open Court 10/25/2010. (nmf) (Entered: 10/25/2010) Minute Entry for proceedings held before Judge Sue L. Robinson: Jury Trial Day 1 held on 10/25/2010. (Court Reporter Valerie Gunning, Brian Gaffigan.) (dlk) (Entered: 10/26/2010)
	D636	PLAINTIFF'S BENCH MEMORANDUM. Filed in Court 10/26/2010. (nmf) (Entered: 10/26/2010) Minute Entry for proceedings held before Judge Sue L. Robinson - Jury Trial (Day 2) held on 10/26/2010. (Court Reporter Valerie Gunning, Kevin Maurer.) (dlk) (Entered: 10/26/2010) Minute Entry for proceedings held before Judge Sue L. Robinson - Jury Trial - Day 3, held on 10/27/2010. (Court Reporter Valerie Gunning/Kevin Maurer.) (nms) (Entered: 10/27/2010)
	D637	STATEMENT -- BENCH MEMORANDUM SUPPORTING MEMC'S PROFFER OF ADMISSIONS BY SOITEC IN PRIOR LAWSUIT INVOLVING THE '564 PATENT submitted at trial by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit A)(Rogowski, Patricia) (Entered: 10/28/2010) Minute Entry for proceedings held before Judge Sue L. Robinson - Jury Trial - Day 4 held on 10/28/2010. (Court Reporter Valerie Gunning/Kevin Maurer.) (nms) (Entered: 11/01/2010)
	D638	Final Jury Instructions read in open Court by Judge Robinson. (lid) (Entered: 11/01/2010) Minute Entry for proceedings held before Judge Sue L. Robinson - Jury Trial held on 11/1/2010. (DAY 5) (Court Reporter V. Gunning.) (lid) (Entered: 11/02/2010) Minute Entry for proceedings held before Judge Sue L. Robinson - Jury Trial completed on 11/2/2010. (DAY 6) (Court Reporter V. Gunning.) (lid) (Entered: 11/02/2010)

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
D639	REDACTED VERSION of <u>342</u> Jury Verdict. (lid) (Entered: 11/02/2010)	
D640	STATEMENT Bench Memorandum in Support of Plaintiffs' Motion For Judgment as a Matter of Law of No Unenforceability of the '009 Patent Due To Inequitable Conduct submitted at trial by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 11/02/2010)	
D641	ANSWERING BRIEF in Opposition re <u>301</u> SEALED MOTION for Reconsideration Request to Modify Protective Order (MEMC'S OPPOSITION TO PLAINTIFFS' MOTION FOR REARGUMENT RE: MODIFICATION OF THE PROTECTIVE ORDER) filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 11/22/2010. (Attachments: # <u>1</u> Exhibit 1 through 5, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 11/12/2010)	
D642	JUDGMENT in favor of defendant MEMC Electronic Materials, Inc. and against plaintiffs S.O.I.TEC Silicon On Insulator Technologies, S.A. and Commissariat a L'Energie Atomique et aux Energies Alternatives as to the 812 patent. IT IS FURTHER ORDERED that judgment be and is hereby entered in favor of plaintiffs S.O.I.TEC Silicon On Insulator Technologies, S.A. and Commissariat a L'Energie Atomique et aux Energies Alternatives and against defendant MEMC Electronic Materials, Inc. as to the 009 patent. Signed by Judge Sue L. Robinson on 11/15/2010. (nmf) (Entered: 11/15/2010)	
D643	STIPULATION Setting Post-Trial Briefing Schedule re <u>348</u> Judgment,, by Commissariat a L'Energie Atomique, MEMC Electronic Materials Inc., SOITEC Silicon On Insulator Technologies SA. (Rogowski, Patricia) (Entered: 11/15/2010)	
D644	MOTION for Reargument re <u>348</u> Judgment,, (MEMCS MOTION FOR REARGUMENT OF THE COURTS ORDER RE: THE UNENFORCEABILITY OF THE 009 PATENT) - filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1)(Rogowski, Patricia) (Entered: 11/16/2010) SO ORDERED- re <u>349</u> Stipulation. Set POST TRIAL Briefing Schedule: (Opening Brief due 12/8/2010., Answering Brief due 12/29/2010., Reply Brief due 1/12/2010.). Signed by Judge Sue L. Robinson on 11/17/2010. (lid) (Entered: 11/17/2010)	
D645	MOTION for Leave to File Reply in Support of Plaintiff's Motion for Reargument - filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 11/23/2010)	

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
	D646	OPENING BRIEF in Support re <u>301</u> SEALED MOTION for Reconsideration Request to Modify Protective Order, <u>351</u> MOTION for Leave to File Reply in Support of Plaintiff's Motion for Reargument filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. Answering Brief/Response due date per Local Rules is 12/10/2010. (Attachments: # <u>1</u> Appendix A, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 11/23/2010)
	D647	STIPULATION TO EXTEND TIME Respond to MEMC's Motion for Reargument of the Court's Order Re: Unenforceability of the '009 Patent to December 3, 2010 - filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 11/24/2010) SO ORDERED- re <u>353</u> STIPULATION TO EXTEND TIME. Set Briefing Schedule: re <u>350</u> MOTION for Reargument re <u>348</u> Judgment.. (Answering Brief due 12/3/2010.). Signed by Judge Sue L. Robinson on 11/30/2010. (lid) (Entered: 11/30/2010)
	D648	STIPULATION TO EXTEND TIME to file Motions and Opening Post-Trial Briefs to December 13, 2010 - filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 12/03/2010)
	D649	REPLY BRIEF re <u>350</u> MOTION for Reargument re <u>348</u> Judgment,, (MEMCS MOTION FOR REARGUMENT OF THE COURTS ORDER RE: THE UNENFORCEABILITY OF THE 009 PATENT) Plaintiffs' Opposition to MEMC's Motion For Reargument of the Court's Order Re: The Unenforceability of the '009 Patent filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 12/03/2010) SO ORDERED- re <u>354</u> STIPULATION TO EXTEND TIME. Set Briefing Schedule: (POST TRIAL Opening Brief due 12/13/2010.). Signed by Judge Sue L. Robinson on 12/6/2010. (lid) (Entered: 12/06/2010)
	D650	EXHIBIT re <u>355</u> Reply Brief, Exhibit B to Plaintiffs' Opposition to MEMC's Motion For Reargument of the Court's Order Re: The Unenforceability of the '009 Patent by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 12/06/2010)
	D651	ANSWERING BRIEF in Opposition re <u>351</u> MOTION for Leave to File Reply in Support of Plaintiff's Motion for Reargument filed by MEMC Electronic Materials Inc.. Reply Brief due date per Local Rules is 12/20/2010. (Rogowski, Patricia) (Entered: 12/10/2010)

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
	D652	STIPULATION TO EXTEND TIME Stipulation and Order for Plaintiffs to file Motions and Opening Post-Trial Briefs to December 14, 2010 - filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 12/13/2010)
	D653	MOTION for Judgment as a Matter of Law - MEMC'S RENEWED MOTION FOR JUDGMENT AS A MATTER OF LAW OR IN THE ALTERNATIVE FOR A NEW TRIAL - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 12/13/2010)
	D654	OPENING BRIEF in Support re <u>359</u> MOTION for Judgment as a Matter of Law - MEMC'S RENEWED MOTION FOR JUDGMENT AS A MATTER OF LAW OR IN THE ALTERNATIVE FOR A NEW TRIAL filed by MEMC Electronic Materials Inc.. Answering Brief/Response due date per Local Rules is 12/30/2010. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 12/13/2010)
	D655	MOTION for Judgment as a Matter of Law Plaintiffs' Renewed Motion For Judgment As A Matter of Law Or In The Alternative For A New Trial - filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 12/14/2010)
	D656	OPENING BRIEF in Support re <u>361</u> MOTION for Judgment as a Matter of Law Plaintiffs' Renewed Motion For Judgment As A Matter of Law Or In The Alternative For A New Trial filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. Answering Brief/Response due date per Local Rules is 1/3/2011. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 12/14/2010)
	D657	MOTION For Injunctive Relief Plaintiffs' Motion For Injunctive Relief And To Lift Stay on Damages Discovery - filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 12/14/2010)
	D658	STIPULATION TO EXTEND TIME due date for Answering and Reply Post-Trial Briefs to January 7, 2011 for Answering Brief and January 21, 2011 for Reply Brief - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 12/15/2010) SO ORDERED- re <u>365</u> STIPULATION TO EXTEND TIME. Set Briefing Schedule: (Answering Post trial Brief due 1/7/2011., Reply post trial Brief due 1/21/2011.). Signed by Judge Sue L. Robinson on 12/16/2010. (lid) (Entered: 12/17/2010)
	D659	STIPULATION TO EXTEND TIME Post-Trial Answering Briefs to January 12, 2011 - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 01/06/2011)

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
	D660	NOTICE of Appearance by Aleine Michelle Porterfield on behalf of Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc. (Attachments: # <u>1</u> Certificate of Service)(Porterfield, Aleine) (Entered: 01/07/2011)
	D661	Joint STIPULATION TO EXTEND TIME Post-trial Answering Briefs and Post-trial Reply Briefs to January 14, 2011 and January 28, 2011 - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 01/12/2011)
	D662	ANSWERING BRIEF in Opposition re <u>359</u> MOTION for Judgment as a Matter of Law - MEMC'S RENEWED MOTION FOR JUDGMENT AS A MATTER OF LAW OR IN THE ALTERNATIVE FOR A NEW TRIAL filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc..Reply Brief due date per Local Rules is 1/24/2011. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 01/14/2011).
	D663	ANSWERING BRIEF in Opposition re <u>361</u> MOTION for Judgment as a Matter of Law Plaintiffs' Renewed Motion For Judgment As A Matter of Law Or In The Alternative For A New Trial (MEMCS ANSWERING BRIEF IN OPPOSITION TO PLAINTIFFS RENEWED MOTION FOR JUDGMENT AS A MATTER OF LAW OR IN THE ALTERNATIVE FOR A NEW TRIAL) filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 1/24/2011. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 01/14/2011).
	D664	DECLARATION re <u>378</u> Answering Brief in Opposition, (DECLARATION OF ROBERT M. EVANS, JR. IN SUPPORT OF MEMCS OPPOSITION TO PLAINTIFFS RENEWED MOTION FOR JUDGMENT AS A MATTER OF LAW OR IN THE ALTERNATIVE FOR A NEW TRIAL) by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Exhibit 2, # <u>3</u> Certificate of Service)(Rogowski, Patricia) (Entered: 01/14/2011)
	D665	REDACTED VERSION of <u>376</u> Answering Brief in Opposition, to Plaintiffs' Motion for Injunctive Relief and to Lift Stay on Damages Discovery by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 01/20/2011)
	D666	REDACTED VERSION of <u>377</u> Appendix to MEMC's Answering Brief in Opposition to Plaintiffs' Motion for Injunctive Relief and to Lift Stay on Damages Discovery by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1-7, # <u>2</u> Exhibit 8, # <u>3</u> Exhibit 9, # <u>4</u> Exhibit 10, # <u>5</u> Exhibit 11, # <u>6</u> Exhibit 12-13, # <u>7</u> Exhibit 14, # <u>8</u> Exhibit 15, # <u>9</u> Exhibit 16, # <u>10</u> Exhibit 17, # <u>11</u> Exhibit 18, # <u>12</u> Exhibit 19, # <u>13</u> Certificate of Service)(Rogowski, Patricia) (Entered: 01/20/2011)

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
	D667	Joint STIPULATION TO EXTEND TIME of Post-Trial Reply Briefs to Tuesday, February 1, 2011 - filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 01/28/2011)
	D668	Joint STIPULATION TO EXTEND TIME of Post-Trial Reply Briefs to Friday, February 4, 2011 - filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 01/31/2011)
	D669	REDACTED VERSION of <u>364</u> Opening Brief in Support,,, Redacted Version of Opening Brief in Support of Plaintiffs' Motion For Injunctive Relief And To Lift Stay on Damages Discovery by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Exhibit B, # <u>3</u> Exhibit C, # <u>4</u> Exhibit D, # <u>5</u> Exhibit E, # <u>6</u> Exhibit F, # <u>7</u> Exhibit G, # <u>8</u> Exhibit H, # <u>9</u> Exhibit I, # <u>10</u> Exhibit J, # <u>11</u> Exhibit K, # <u>12</u> Exhibit L, # <u>13</u> Exhibit M, # <u>14</u> Exhibit N, # <u>15</u> Exhibit O, # <u>16</u> Exhibit P, # <u>17</u> Exhibit Q, # <u>18</u> Exhibit R, # <u>19</u> Exhibit S)(Kraft, Denise) (Entered: 02/02/2011)
	D670	REPLY BRIEF re <u>359</u> MOTION for Judgment as a Matter of Law - MEMC'S RENEWED MOTION FOR JUDGMENT AS A MATTER OF LAW OR IN THE ALTERNATIVE FOR A NEW TRIAL filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 02/04/2011)
	D671	REPLY BRIEF re <u>361</u> MOTION for Judgment as a Matter of Law Plaintiffs' Renewed Motion For Judgment As A Matter of Law Or In The Alternative For A New Trial filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 02/04/2011)
	D672	DECLARATION re <u>387</u> Reply Brief, Declaration of Michael L. Brody in Support of Reply Brief In Support of Plaintiffs' Renewed Motion For Judgment as a Matter of Law or In The Alternative For a New Trial by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 02/04/2011)
	D673	MOTION to Strike <u>386</u> Reply Brief, Motion By Plaintiffs' To Strike Reply Brief In Support of MEMC's Renewed Motion For Judgment as a Matter of Law or, In The Alternative, a New Trial (D.I. 386) - filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 02/08/2011)

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
	D674	OPENING BRIEF in Support re <u>390</u> MOTION to Strike <u>386</u> Reply Brief, Motion By Plaintiffs' To Strike Reply Brief In Support of MEMC's Renewed Motion For Judgment as a Matter of Law or, In The Alternative, a New Trial (D.I. 386) MOTION to Strike <u>386</u> Reply Brief, Motion By Plaintiffs' To Strike Reply Brief In Support of MEMC's Renewed Motion For Judgment as a Matter of Law or, In The Alternative, a New Trial (D.I. 386) filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc..Answering Brief/Response due date per Local Rules is 2/25/2011. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 02/08/2011)
	D675	DECLARATION re <u>391</u> Opening Brief in Support,, Declaration of Marcus T. Hall in Support of Plaintiffs' Opening Brief in Support of Motion to Strike Reply Brief In Support of MEMC's Renewed Motion For Judgment as a Matter of Law or, In The Alternative, a New Trial (D.I. 386) by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 02/08/2011)
	D676	REDACTED VERSION of <u>389</u> Reply Brief, Redacted Version of Reply Brief in Support of Plaintiffs' Motion For Injunctive Relief And To Lift Stay on Damages Discovery by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 02/09/2011)

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.